



ANSI C63.19

TEST REPORT

Product Name	HSDPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth;
Model Name	HUAWEI U8651T, U8651T, U8651, Astro
FCC ID	QISU8651T
Client	Huawei Technologies Co., Ltd.

TA Technology (Shanghai) Co., Ltd.

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GENERAL SUMMARY

Product Name	HSDPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth;	Model	HUAWEI U8651T, U8651T, U8651, Astro
Report No.	RZA1201-0064HAC01R2	FCC ID	QISU8651T
Client	Huawei Technologies Co., Ltd.		
Manufacturer	Huawei Technologies Co., Ltd.		
Reference Standard(s)	ANSI C63.19-2007: American National Standard Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.		
Conclusion	This portable wireless equipment has been measured in all cases requested by the relevant standards. General Judgment: M3 (RF Emission)  (Stamp) Date of issue: March 2nd, 2012		
Comment	The test result only responds to the measured sample.		

Approved by 杨伟中
Director

Revised by 凌敏宝
SAR Manager

Performed by 秦明
SAR Engineer

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1. General Information

1.1. Notes of the Test Report

TA Technology (Shanghai) Co., Ltd. guarantees the reliability of the data presented in this test report, which is the results of measurements and tests performed for the items under test on the date and under the conditions stated in this test report and is based on the knowledge and technical facilities available at TA Technology (Shanghai) Co., Ltd. at the time of execution of the test.

TA Technology (Shanghai) Co., Ltd. is liable to the client for the maintenance by its personnel of the confidentiality of all information related to the items under test and the results of the test. This report only refers to the item that has undergone the test.

This report standalone dose not constitute or imply by its own an approval of the product by the certification Bodies or competent Authorities. This report cannot be used partially or in full for publicity and/or promotional purposes without previous written approval of **TA Technology (Shanghai) Co., Ltd.** and the Accreditation Bodies, if it applies.

If the electrical report is inconsistent with the printed one, it should be subject to the latter.

1.2. Testing Laboratory

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1.3. Applicant Information

Company: Huawei Technologies Co., Ltd.
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City: Shenzhen
Postal Code: 518129
Country: P.R. China
Contact: Zhao Guiying
Telephone: 0755-28780808
Fax: 0755-28780808

1.4. Manufacturer Information

Company: Huawei Technologies Co., Ltd.
Address: Bantian, Longgang District
City: Shenzhen
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1.5. Information of EUT

General Information

Device Type:	Portable Device		
Product Name:	HSDPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth;		
IMEI:	004401720342068		
Hardware Version:	HD4U865M		
Software Version:	U8651V100R001USAC85B865SP01		
Antenna Type:	Internal Antenna		
Device Operating Configurations:			
Supporting Mode(s):	GSM 850/ GSM 1900; (tested)		
	WCDMA Band II/ WCDMA Band IV/WCDMA Band V; (tested)		
	GSM900/GSM1800; (untested)		
	WiFi (802.11b/g/n); (untested)		
	Bluetooth; (untested)		
Test Modulation:	(GSM)GMSK; (WCDMA) QPSK		
Device Class:	B		
HSDPA UE Category:	8		
GPRS Multislot Class(10):	Max Number of Timeslots in Uplink	2	
	Max Number of Timeslots in Downlink	4	
	Max Total Timeslot	5	
EGPRS Multislot Class(10):	Max Number of Timeslots in Uplink	2	
	Max Number of Timeslots in Downlink	4	
	Max Total Timeslot	5	
Operating Frequency Range(s):	Mode	Tx (MHz)	Rx (MHz)
	GSM 850	824.2 ~ 848.8	869.2 ~ 893.8
	GSM 1900	1850.2 ~ 1909.8	1930.2 ~ 1989.8
	WCDMA Band II	1852.4 ~ 1907.6	1932.4 ~ 1987.6
	WCDMA Band IV	1712.4 ~ 1752.6	2112.4 ~ 2152.2
	WCDMA Band V	826.4 ~ 846.6	871.4 ~ 891.6
Test Channel: (Low - Middle - High)	128-190-251 (GSM 850) (tested) 512-661-810 (GSM 1900) (tested) 9262 - 9400 - 9538 (WCDMA Band II) (tested) 1312-1413-1513 (WCDMA Band IV) (tested) 4132 - 4183 - 4233 (WCDMA Band V) (tested)		
Power Class:	GSM 850: 4, tested with power level 5		
	GSM 1900: 1, tested with power level 0		
	WCDMA Band II: 3, tested with power control all up bits		
	WCDMA Band IV: 3, tested with power control all up bits		
	WCDMA Band V: 3, tested with power control all up bits		

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Auxiliary Equipment Details

AE:Battery

Model: HB5K1H

Manufacturer: Huawei Technologies Co., Ltd.

S/N: WHCB912HI36J7417

Equipment Under Test (EUT) is a model of HSDPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth;. The detail about Mobile phone and Lithium Battery is in chapter 1.5 in this report. It has Personal Wireless Routers (hot spots) function, WIFI calling function and Proximity Sensor function. HAC is tested for GSM 850, GSM 1900, WCDMA Band II, WCDMA Band IV and WCDMA Band V. The device has an internal antenna for GSM/WCDMA Tx/Rx, and the other is BT/WIFI antenna that is used for Tx/Rx.

The sample under test was selected by the Client.

Components list please refer to documents of the manufacturer.

Air-Interface	Band (MHz)	Type	C63.19/ tested	Simultaneous Transmissions Note: Not to be tested	Concurrent single transmission	Reduced power 20.19(c)(1)	Voice Over Digital Transport (Data)
GSM	850	VO	Yes	Yes WIFI or BT	Yes: GPRS/EDGE,WIFI, BT	NO	NA
	1900	VO	Yes		Not rated	NO	NA
	GPRS/EDGE	DT	NA	Yes BT	Yes: *see note	NA	NA
WCDMA	850	VO	Yes	Yes WIFI or BT	Yes: WIFI,HSDPA,BT Not rated	NA	NA
	1700	VO	Yes				
	1900	VO	Yes				
	HSDPA	DT	NA	Yes BT	Yes: *see note	NA	NA
WIFI	2400	DT	NA	Yes GSM or BT or WCDMA	NA	NA	Yes
Bluetooth (BT)	2400	DT	NA	Yes GSM or WIFI or WCDMA	NA	NA	NA

VO Voice CMRS/PSTN Service only

V/D Voice CMRS/PSTN and Data Service

DT Digital Transport

*HAC Rating was based on concurrent voice and data modes, Non current mode was found to represent worst case rating for both M and T rating

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1.6. The Ambient Conditions during Test

Temperature	Min. = 18°C, Max. = 28 °C
Relative humidity	Min. = 0%, Max. = 80%
Ground system resistance	< 0.5 Ω
Ambient noise is checked and found very low and in compliance with requirement of standards. Reflection of surrounding objects is minimized and in compliance with requirement of standards.	

1.7. The Total M-rating of each tested band

Mode	Rating
GSM 850	M3
GSM 1900	M3
WCDMA Band II	M4
WCDMA Band IV	M4
WCDMA Band V	M4

1.8. Test Date

The test is performed on January 16, 2012.

2. Test Information

2.1. Operational Conditions during Test

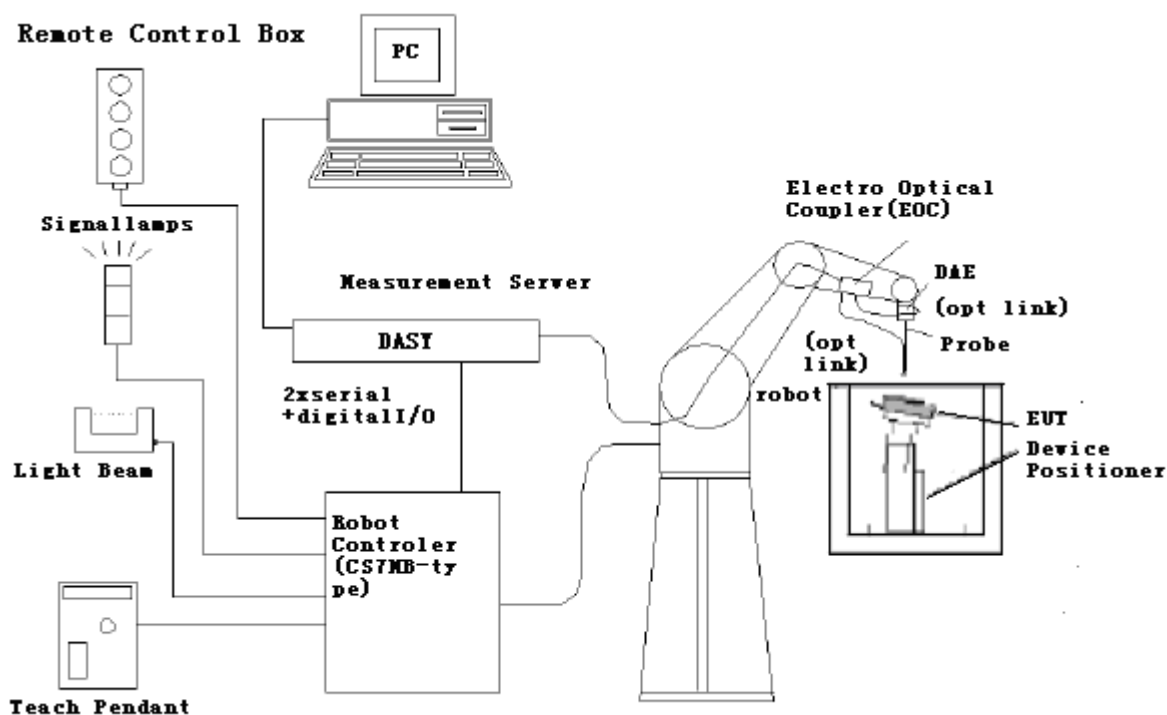
2.1.1. General Description of Test Procedures

The phone was tested in all normal configurations for the ear use. The EUT is mounted in the device holder equivalent as for classic dosimeter measurements. The acoustic output of the EUT shall coincide with the center point of the area formed by the dielectric wire and the middle bar of the arch's top frame. The EUT shall be moved vertically upwards until it touches the frame. The fine adjustment is possible by sliding the complete. The EUT holder is on the yellow base plate of the Test Arch phantom. These test configurations are tested at the high, middle and low frequency channels of each applicable operating mode; for example, GSM, WCDMA (UMTS), CDMA and TDMA.

2.1.2. GSM/WCDMA Test Configuration

A communication link is set up with a System Simulator (SS) by air link, and a call is established. The Absolute Radiofrequency Channel Number (ARFCN) is allocated to 128, 190 and 251 in the case of GSM 850, to 512, 661 and 810 in the case of GSM 1900, to 9262, 9400 and 9538 in the case of WCDMA Band II, to 1312, 1413 and 1513 in the case of WCDMA Band IV, to 4132, 4183 and 4233 in the case of WCDMA Band V. The EUT is commanded to operate at maximum transmitting power. Using E5515C the power lever is set to "5" in SAR of GSM 850, set to "0" in SAR of GSM 1900. Set to all up bits for WCDMA. The test in the bands of GSM 850/GSM 1900 and WCDMA Band II/WCDMA Band IV/WCDMA Band V are performed in the mode of speech transfer function.

These measurements are performed using the DASY4 automated dosimetric assessment system. It is made by Schmid & Partner Engineering AG (SPEAG) in Zurich, Switzerland. It consists of high precision robotics system (Stäubli), robot controller, Intel Core2 computer, near-field probe, probe alignment sensor. The robot is a six-axis industrial robot performing precise movements. Cell controller systems contain the power supply, robot controller, teach pendant (Joystick) and remote control, and are used to drive the robot motors. The Stäubli Robot is connected to the cell controller to allow software manipulation of the robot. A data acquisition electronic (DAE) circuit performs the signal amplification; signal multiplexing, AD-conversion, offset measurements, mechanical surface detection, collision detection, etc. is connected to the Electro-optical coupler (EOC). The EOC performs the conversion from the optical into digital electric signal of the DAE and transfers data to the PC plug-in card.



The DAE4 consists of a highly sensitive electrometer-grade preamplifier with auto-zeroing, a channel and gain-switching multiplexer, a fast 16 bit AD-converter and a command decoder and control logic unit. Transmission to the PC-card is accomplished through an optical downlink for data and status information and an optical uplink for commands and clock lines. The mechanical probe mounting device includes two different sensor systems for frontal and sidewise probe contacts. They are also used for mechanical surface detection and probe collision detection. The robot uses its own controller with a built in VME-bus computer.

2.2.2. Probe System

The HAC measurements were conducted with the E-Field Probe ER3DV6 and the H-Field Probe H3DV6 (manufactured by SPEAG), designed in the classical triangular configuration and optimized for dosimetric evaluation.

E-Field Probe Description

Construction	One dipole parallel, two dipoles normal to probe axis Built-in shielding against static charges PEEK enclosure material
Calibration	In air from 100 MHz to 3.0 GHz (absolute accuracy $\pm 6.0\%$, $k=2$)
Frequency	40 MHz to > 6 GHz (can be extended to < 20 MHz) Linearity: ± 0.2 dB (100 MHz to 3 GHz)
Directivity	± 0.2 dB in air (rotation around probe axis) ± 0.4 dB in air (rotation normal to probe axis)
Dynamic Range	2 V/m to > 1000 V/m; Linearity: ± 0.2 dB
Dimensions	Overall length: 330 mm (Tip: 16 mm) Tip diameter: 8 mm (Body: 12 mm) Distance from probe tip to dipole centers: 2.5 mm
Application	General near-field measurements up to 6 GHz Field component measurements Fast automatic scanning in phantoms



Figure 2 ER3DV6 E-field Probe

H-Field Probe Description

Construction	Three concentric loop sensors with 3.8 mm loop diameters Resistively loaded detector diodes for linear response Built-in shielding against static charges PEEK enclosure material (resistant to organic solvents, e.g., glycolether)
Frequency	200 MHz to 3 GHz (absolute accuracy $\pm 6.0\%$, $k=2$); Output linearized
Directivity	± 0.2 dB (spherical isotropy error)
Dynamic Range	10 mA/m to 2 A/m at 1 GHz
E-Field Interference	< 10% at 3 GHz (for plane wave)
Dimensions	Overall length: 330 mm (Tip: 40 mm) Tip diameter: 6 mm (Body: 12 mm) Distance from probe tip to dipole centers: 3 mm



Figure 3 H3DV6 H-field Probe

Application	General magnetic near-field measurements up to 3 GHz (in air or liquids) Field component measurements Surface current measurements Low interaction with the measured field
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2.2.3. Test Arch Phantom & Phone Positioner

The Test Arch phantom should be positioned horizontally on a stable surface. Reference markings on the Phantom allow the complete setup of all predefined phantom positions and measurement grids by manually teaching three points in the robot. It enables easy and well defined positioning of the phone and validation dipoles as well as simple teaching of the robot (Dimensions: 370 x 370 x 370 mm).

The Device reference point is set for the EUT at 6.3 mm, the Grid reference point is on the upper surface at the origin of the coordinates, and the “user point \Height Check 0.5 mm” is 0.5mm above the center, allowing verification of the gap of 0.5mm while the probe is positioned there.

The Phone Positioner supports accurate and reliable positioning of any phone with effect on near field $<\pm 0.5$ dB.

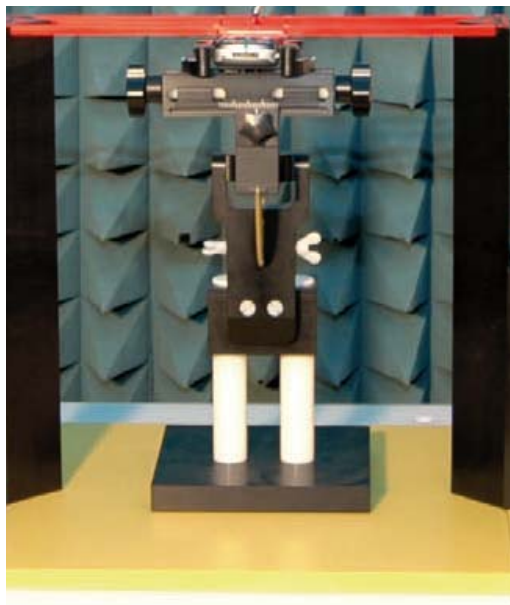


Figure 4 HAC Phantom & Device Holder

2.3. RF Test Procedures

The evaluation was performed with the following procedure:

1. Confirm proper operation of the field probe, probe measurement system and other instrumentation and the positioning system.
2. Position the WD in its intended test position. The gauge block can simplify this positioning. Note that a separate E-field and H-field gauge block will be needed if the center of the probe sensor elements is at different distances from the tip of the probe.
3. Configure the WD normal operation for maximum rated RF output power, at the desired channel and other operating parameters (e.g., test mode), as intended for the test.
4. The center sub-grid shall center on the center of the axial measurement point or the acoustic output, as appropriate. Locate the field probe at the initial test position in the 50 mm by 50 mm grid, which is contained in the measurement plane. If the field alignment method is used, align the probe for maximum field reception.
5. Record the reading.
6. Scan the entire 50 mm by 50 mm region in equally spaced increments and record the reading at each measurement point. The grid is 5 cm by 5 cm area that is divided into 9 evenly sized blocks or sub-grids. The distance between measurement points shall be sufficient to assure the identification of the maximum reading.
7. Identify the five contiguous sub-grids around the center sub-grid with the lowest maximum field strength readings. Thus the six areas to be used to determine the WD's highest emissions are identified and outlined for the final manual scan. Please note that a maximum of five blocks can be excluded for both E-field and H-field measurements for the WD output being measured. Stated another way, the center sub-grid and three others must be common to both the E-field and H-field measurements.
8. Identify the maximum field reading within the non-excluded sub-grids identified in Step 7.
9. Convert the maximum field strength reading identified in Step 8 to V/m or A/m, as appropriate. For probes which require a probe modulation factor, this conversion shall be done using the appropriate probe modulation factor and the calibration.
10. Repeat Step 1 through Step 10 for both the E-field and H-field measurements.
11. Compare this reading to the categories in ANSI C63.19 Clause 7 and record the resulting category. The lowest category number listed in 7.2, Table 7.4, or Table 7.5 obtained in Step 10 for either E- or H-field determines the M category for the audio coupling mode assessment. Record the WD category rating.

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Figure 5 WD reference and plane for RF emission measurements

2.4. System Check

Validation Procedure

Place a dipole antenna meeting the requirements given in ANSI C63.19 D.5 in the position normally occupied by the WD. The dipole antenna serves as a known source for an electrical and magnetic output. Position the E-field and H-field probes so that:

The probes and their cables are parallel to the coaxial feed of the dipole antenna.

The probe cables and the coaxial feed of the dipole antenna approach the measurement area from opposite directions.

The center point of the probe element(s) are 10 mm from the closest surface of the dipole elements. Validation was performed to verify that measured E-field and H-field values are within +/-25% from the target reference values provided by the manufacturer. "Values within +/-25% are acceptable. Of which 12% is deviation and 13% is measurement uncertainty."

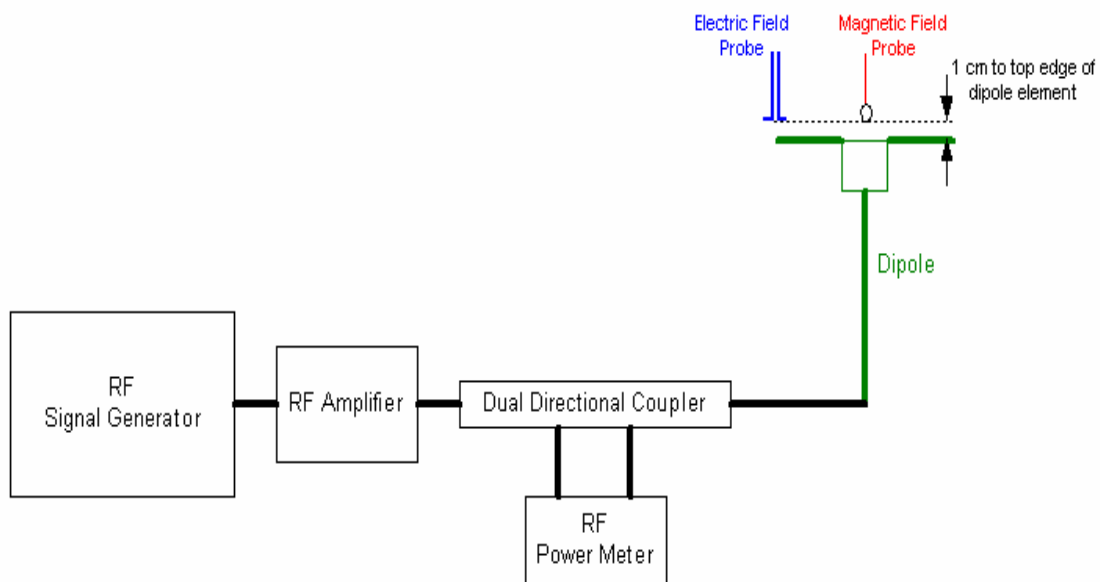


Figure 6 Dipole Validation Setup

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Dipole Measurement Summary

E-Field Scan					
Mode	Frequency (MHz)	Input Power (mW)	Value		Test Date
CW	835	100	Target ¹ Value(V/m)	158.2	/
			Measured ² Value(V/m)	159.0	January 16, 2012
			Deviation ³ (%)	-0.51	/
CW	1880	100	Target ¹ Value(V/m)	140.5	/
			Measured ² Value(V/m)	138.1	January 16, 2012
			Deviation ³ (%)	1.71	/
H-Field Scan					
Mode	Frequency (MHz)	Input Power (mW)	Value		Test Date
CW	835	100	Target ¹ Value(V/m)	0.446	/
			Measured ² Value(V/m)	0.455	January 16, 2012
			Deviation ³ (%)	-2.02	/
CW	1880	100	Target ¹ Value(V/m)	0.468	/
			Measured ² Value(V/m)	0.462	January 16, 2012
			Deviation ³ (%)	1.28	/

Notes: 1. Target value is provided by SPEAD in the calibration certificate of specific dipoles.

2. Please refer to the attachment for detailed measurement data and plot.

3. Deviation (%) = 100 * (Target value minus Measured value) divided by Target value.

2.5. Probe Modulation Factor

The Probe Modulation Factor (PMF) is defined as the ratio of the field readings for a CW and a modulated signal with the equivalent Field Envelope Peak as defined in ANSI C63.19 (Chapter C.3.1). Calibration shall be made of the modulation response of the probe and its instrumentation chain. This Calibration shall be performed with the field probe, attached to the instrumentation that is to be used with it during the measurement. The response of the probe system to a CW field at the frequency(s) of interest is compared to its response to a modulated signal with equal peak amplitude. The field level of the test signals shall be more than 10dB above the ambient level and the noise floor of the instrumentation being used. The ratio of the CW reading to that taken with a modulated field shall be applied to the readings taken of modulated fields of the specified type.

Modulation Factor Test Procedure

This may be done using the following procedure:

1. Fix the field probe in a set location relative to a field generating device, such as the reference dipole antenna.
2. Illuminate the probe using the wireless device connected to the reference dipole with a test signal at the intended measurement frequency, Ensure there is sufficient field coupling between the probe and the antenna so the resulting reading is greater than 10 dB above the probe system noise floor but within the systems operating range.
3. Record the amplitude applied to the antenna during transmission and the field strength measured by the E-field probe located near the tip of the dipole antenna
4. Replace the wireless device with an RF signal generator producing an unmodulated CW signal and set to the wireless device operating frequency.
5. Set the amplitude of the unmodulated signal to equal that recorded from the wireless device.
6. Record the reading of the probe measurement system of the unmodulated signal.
7. The ratio, in linear units, of the probe reading in Step 6 to the reading in Step 3 is the E-field modulation factor. $PMF_E = E_{CW} / E_{mod}$ ($PMF_H = H_{CW} / H_{mod}$)
8. Repeat the previous steps using the H-field probe, except locate the probe at the center of the dipole.

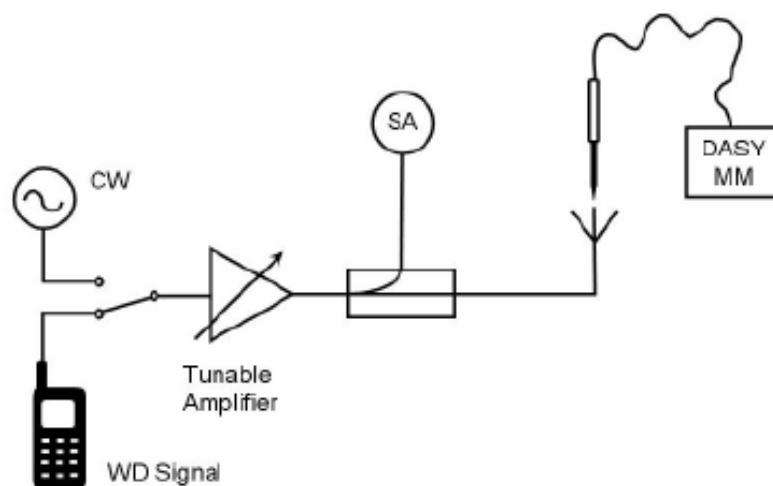


Figure 7 Probe Modulation Factor Test Setup

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PMF

Band	E-Field Probe Modulation Factor	H-Field Probe Modulation Factor
GSM 850	2.81	2.75
GSM 1900	2.84	2.84
WCDMA Band II	1.02	1.01
WCDMA Band IV	1.02	1.01
WCDMA Band V	1.03	1.01

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2.6. Conducted Output Power Measurement

Summary

The DUT is tested using an E5515C communications tester as controller unit to set test channels and maximum output power to the DUT, as well as for measuring the conducted power. Conducted output power was measured using an integrated RF connector and attached RF cable. This result contains conducted output power for the EUT.

Conducted Power Results

GSM 850	Conducted Power(dBm)		
	Channel 128	Channel 190	Channel 251
Test Results	31.51	31.61	31.63
GSM 1900	Conducted Power(dBm)		
	Channel 512	Channel 661	Channel 810
Test Results	30.11	29.88	29.78
WCDMA Band II	Conducted Power(dBm)		
	Channel 9262	Channel 9400	Channel 9538
12.2kbps RMC	22.57	23.05	22.62
64kbps RMC	22.51	23.04	22.65
144kbps RMC	22.48	23.06	22.6
384kbps RMC	22.51	23.04	22.6
WCDMA Band II HSDPA	Conducted Power(dBm)		
	Channel 9262	Channel 9400	Channel 9538
Sub - Test 1	22.45	23.02	22.58
Sub - Test 2	22.15	22.73	22.32
Sub - Test 3	21.93	22.52	22.15
Sub - Test 4	21.57	22.06	22.18
WCDMA Band IV	Conducted Power(dBm)		
	Channel 1312	Channel 1413	Channel 1513
12.2kbps RMC	23.15	23.25	23.24
64kbps RMC	23.26	23.3	23.21
144kbps RMC	23.18	23.33	23.3

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384kbps RMC	23.26	23.27	23.24
WCDMA Band IV HSDPA	Conducted Power(dBm)		
	Channel 1312	Channel 1413	Channel 1513
Sub - Test 1	23	23.11	23.12
Sub - Test 2	22.62	22.82	22.77
Sub - Test 3	22.11	22.3	22.35
Sub - Test 4	22.08	22.18	22.01
WCDMA Band V	Conducted Power(dBm)		
	Channel 4132	Channel 4183	Channel 4233
12.2kbps RMC	22.17	22.06	22.26
64kbps RMC	22.18	22.03	22.21
144kbps RMC	22.16	22.03	22.16
384kbps RMC	22.2	22.04	22.23
WCDMA Band V HSDPA	Conducted Power(dBm)		
	Channel 4132	Channel 4183	Channel 4233
Sub - Test 1	22.14	21.96	22.11
Sub - Test 2	21.94	21.79	21.95
Sub - Test 3	21.43	21.27	21.47
Sub - Test 4	21.5	21.48	21.44

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3. Test Results

3.1. ANSI C63.19-2007 Limits

Category		Telephone RF parameters < 960 MHz			
Near field	AWF	E-field emissions		H-field emissions	
Category M1/T1	0	631.0 to 1122.0	V/m	1.91 to 3.39	A/m
	-5	473.2 to 841.4	V/m	1.43 to 2.54	A/m
Category M2/T2	0	354.8 to 631.0	V/m	1.07 to 1.91	A/m
	-5	266.1 to 473.2	V/m	0.80 to 1.43	A/m
Category M3/T3	0	199.5 to 354.8	V/m	0.60 to 1.07	A/m
	-5	149.6 to 266.1	V/m	0.45 to 0.80	A/m
Category M4/T4	0	< 199.5	V/m	< 0.60	A/m
	-5	< 149.6	V/m	< 0.45	A/m
Category		Telephone RF parameters > 960 MHz			
Near field	AWF	E-field emissions		H-field emissions	
Category M1/T1	0	199.5 to 354.8	V/m	0.60 to 1.07	A/m
	-5	149.6 to 266.1	V/m	0.45 to 0.80	A/m
Category M2/T2	0	112.2 to 199.5	V/m	0.34 to 0.60	A/m
	-5	84.1 to 149.6	V/m	0.25 to 0.45	A/m
Category M3/T3	0	63.1 to 112.2	V/m	0.19 to 0.34	A/m
	-5	47.3 to 84.1	V/m	0.14 to 0.25	A/m
Category M4/T4	0	< 63.1	V/m	< 0.19	A/m
	-5	< 47.3	V/m	< 0.14	A/m

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3.2. Summary Test Results

GSM 850 Results

E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/251	848.8	187.7	0.055	M3	Figure 12
Middle/190	836.6	183.0	-0.032	M3	Figure 13
Low/128	824.2	145.0	-0.115	M4	Figure 14
H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/251	848.8	0.251	0.030	M4	Figure 15
Middle/190	836.6	0.209	0.136	M4	Figure 16
Low/128	824.2	0.157	0.169	M4	Figure 17

GSM 1900 Results

E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/810	1909.8	69.2	-0.080	M3	Figure 18
Middle/661	1880	66.0	-0.040	M3	Figure 19
Low/512	1850.2	66.2	0.057	M3	Figure 20
H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/810	1909.8	0.208	-0.012	M3	Figure 21
Middle/661	1880	0.192	0.035	M3	Figure 22
Low/512	1850.2	0.201	0.038	M3	Figure 23

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WCDMA Band II Results

WCDMA Band II E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/9538	1907.6	32.3	-0.007	M4	Figure 24
Middle/9400	1880	33.5	-0.005	M4	Figure 25
Low/9262	1852.4	34.6	0.033	M4	Figure 26
WCDMA Band II +HSDPA E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/9538	1907.6	33.6	0.099	M4	Figure 27
Middle/9400	1880	35.6	-0.065	M4	Figure 28
Low/9262	1852.4	36.8	-0.027	M4	Figure 29
WCDMA Band II H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/9538	1907.6	0.097	-0.046	M4	Figure 30
Middle/9400	1880	0.098	0.007	M4	Figure 31
Low/9262	1852.4	0.110	0.040	M4	Figure 32
WCDMA Band II +HSDPA H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/9538	1907.6	0.096	0.042	M4	Figure 33
Middle/9400	1880	0.097	0.160	M4	Figure 34
Low/9262	1852.4	0.109	0.032	M4	Figure 35

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WCDMA Band IV Results

WCDMA Band IV E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/1513	1752.6	40.9	0.027	M4	Figure 36
Middle/1413	1732.6	37.7	0.014	M4	Figure 37
Low/1312	1712.4	40.3	0.016	M4	Figure 38
WCDMA Band IV +HSDPA E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/1513	1752.6	41.3	0.038	M4	Figure 39
Middle/1413	1732.6	38.0	0.059	M4	Figure 40
Low/1312	1712.4	40.4	-0.021	M4	Figure 41
WCDMA Band IV H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/1513	1752.6	0.114	0.087	M4	Figure 42
Middle/1413	1732.6	0.105	0.009	M4	Figure 43
Low/1312	1712.4	0.110	0.088	M4	Figure 44
WCDMA Band IV +HSDPA H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/1513	1752.6	0.113	0.052	M4	Figure 45
Middle/1413	1732.6	0.104	0.033	M4	Figure 46
Low/1312	1712.4	0.109	0.052	M4	Figure 47

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WCDMA Band V Results

WCDMA Band V E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/4233	846.6	65.3	-0.078	M4	Figure 48
Middle/4183	836.6	58.3	0.074	M4	Figure 49
Low/4132	826.4	59.4	-0.033	M4	Figure 50
WCDMA Band V +HSDPA E-Field					
Channel	Frequency (MHz)	Peak Field (V/m)	Power Drift (dB)	Rating	Graph Results
High/4233	846.6	64.7	-0.060	M4	Figure 51
Middle/4183	836.6	58.3	-0.056	M4	Figure 52
Low/4132	826.4	61.2	-0.007	M4	Figure 53
WCDMA Band V H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/4233	846.6	0.086	0.156	M4	Figure 54
Middle/4183	836.6	0.070	0.026	M4	Figure 55
Low/4132	826.4	0.073	0.158	M4	Figure 56
WCDMA Band V +HSDPA H-Field					
Channel	Frequency (MHz)	Peak Field (A/m)	Power Drift (dB)	Rating	Graph Results
High/4233	846.6	0.085	0.016	M4	Figure 57
Middle/4183	836.6	0.070	0.038	M4	Figure 58
Low/4132	826.4	0.072	0.064	M4	Figure 59

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4. Measurement Uncertainty

No.	Error source	Type	Uncertainty Value (%)	Prob. Dist.	k	c_{iE}	c_{iH}	Standard Uncertainty (%) u_i (%) E	Standard Uncertainty (%) u_i (%) H	Degree of freedom V_{eff} or v_i
Measurement System										
1	Probe Calibration	B	5.1	N	1	1	1	5.1	5.1	∞
2	Axial Isotropy	B	4.7	R	$\sqrt{3}$	1	1	2.7	2.7	∞
3	Sensor Displacement	B	16.5	R	$\sqrt{3}$	1	0.145	9.5	1.4	∞
4	Boundary Effects	B	2.4	R	$\sqrt{3}$	1	1	1.4	1.4	∞
5	Linearity	B	4.7	R	$\sqrt{3}$	1	1	2.7	2.7	∞
6	Scaling to Peak Envelope Power	B	2.0	R	$\sqrt{3}$	1	1	1.2	1.2	∞
7	System Detection Limit	B	1.0	R	$\sqrt{3}$	1	1	0.6	0.6	∞
8	Readout Electronics	B	0.3	N	1	1	1	0.3	0.3	∞
9	Response Time	B	0.8	R	$\sqrt{3}$	1	1	0.5	0.5	∞
10	Integration Time	B	2.6	R	$\sqrt{3}$	1	1	1.5	1.5	∞
11	RF Ambient Conditions	B	3.0	R	$\sqrt{3}$	1	1	1.7	1.7	∞
12	RF Reflections	B	12.0	R	$\sqrt{3}$	1	1	6.9	6.9	∞
13	Probe Positioner	B	1.2	R	$\sqrt{3}$	1	0.67	0.7	0.5	∞
14	Probe Positioning	A	4.7	R	$\sqrt{3}$	1	0.67	2.7	1.8	∞
15	Extra. And Interpolation	B	1.0	R	$\sqrt{3}$	1	1	0.6	0.6	∞
Test Sample Related										
16	Device Positioning Vertical	B	4.7	R	$\sqrt{3}$	1	0.67	2.7	1.8	∞
17	Device Positioning Lateral	B	1.0	R	$\sqrt{3}$	1	1	0.6	0.6	∞
18	Device Holder and Phantom	B	2.4	R	$\sqrt{3}$	1	1	1.4	1.4	∞

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19	Power Drift	B	5.0	R	$\sqrt{3}$	1	1	2.9	2.9	∞
Phantom and Setup related										
20s	Phantom Thickness	B	2.4	R	$\sqrt{3}$	1	0.67	1.4	0.9	∞
Combined standard uncertainty(%)								14.7	10.9	
Expanded Std. uncertainty on power (K=2)								29.4	21.8	
Expanded Std. uncertainty on field (K=2)								14.7	10.9	

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5. Main Test Instruments

No.	Name	Type	Serial Number	Calibration Date	Valid Period
01	Power meter	Agilent E4417A	GB41291714	March 12, 2011	One year
02	Power sensor	Agilent N8481H	MY50350004	September 25, 2011	One year
03	Signal Generator	HP 8341B	2730A00804	September 12, 2011	One year
04	Amplifier	IXA-020	0401	No Calibration Requested	
05	BTS	E5515C	MY48360988	December 2, 2011	One year
06	E-Field Probe	ER3DV6	2302	June 15, 2011	One year
07	H-Field Probe	H3DV6	6187	June 17, 2011	One year
08	DAE	DAE4	871	November 22, 2011	One year
09	Validation Kit 835MHz	CD835V3	1133	April 22, 2009	Three years
10	Validation Kit 1880MHz	CD1880V3	1115	April 22, 2009	Three years

*****END OF REPORT BODY*****

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ANNEX A: System Check Results

HAC_System Performance Check at 835MHz_E

DUT: Dipole 835 MHz; Type: CD835V3; SN:1133

Date/Time: 1/16/2012 2:13:32 PM

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 159.0 V/m

Probe Modulation Factor = 1.00

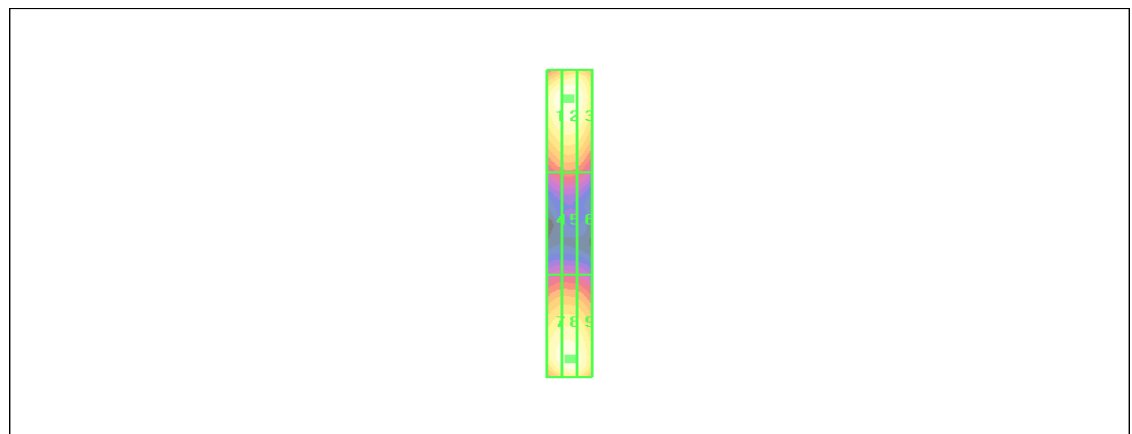
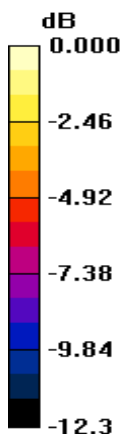
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 105.5 V/m; Power Drift = -0.026 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 158.1 M4	Grid 2 161.0 M4	Grid 3 156.3 M4
Grid 4 86.9 M4	Grid 5 89.2 M4	Grid 6 85.8 M4
Grid 7 155.0 M4	Grid 8 159.0 M4	Grid 9 154.2 M4



0 dB = 161.0V/m

Figure 8 System Performance Check 835MHz_E

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HAC_System Performance Check at 835MHz_H

DUT: Dipole 835 MHz; Type: CD835V3; SN: 1133

Date/Time: 1/16/2012 11:32:58 AM

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole =

10mm/Hearing Aid Compatibility Test (41x361x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.455 A/m

Probe Modulation Factor = 1.00

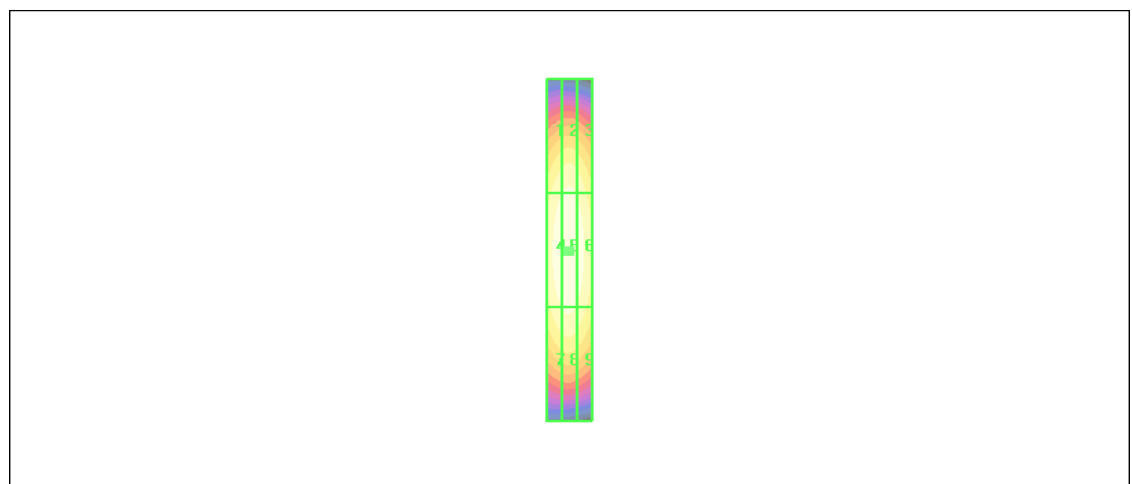
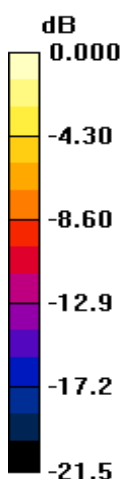
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.485 A/m; Power Drift = -0.005 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.383 M4	Grid 2 0.401 M4	Grid 3 0.376 M4
Grid 4 0.437 M4	Grid 5 0.455 M4	Grid 6 0.429 M4
Grid 7 0.386 M4	Grid 8 0.401 M4	Grid 9 0.377 M4



0 dB = 0.455A/m

Figure 9 System Performance Check 835MHz_H

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HAC_System Performance Check at 1880MHz_E

DUT: Dipole 1880 MHz; Type: CD1880V3; SN: 1115

Date/Time: 1/16/2012 12:50:34 PM

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 138.1 V/m

Probe Modulation Factor = 1.00

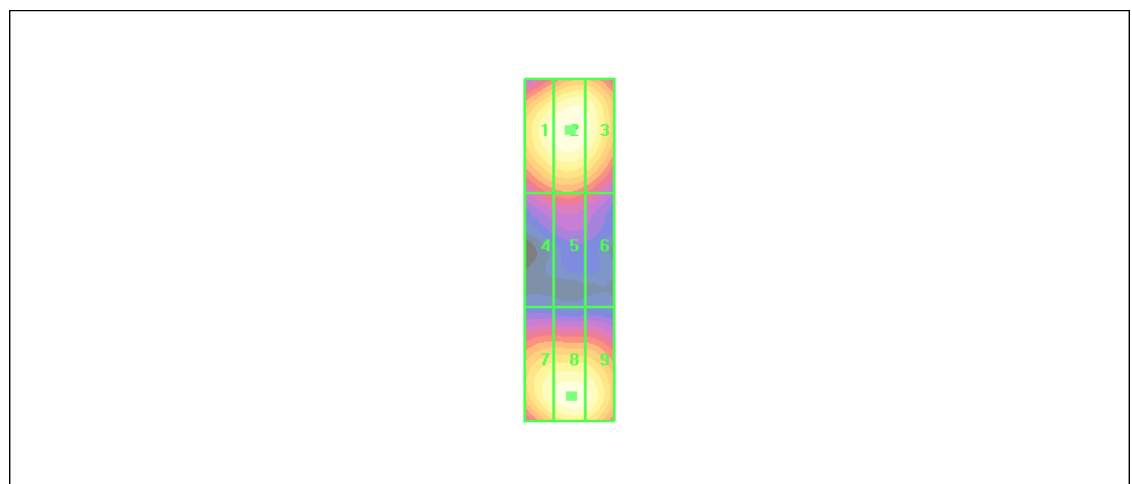
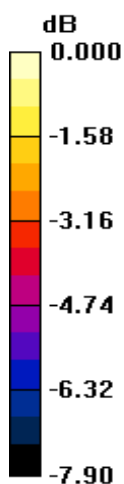
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 156.5 V/m; Power Drift = -0.007 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak E-field in V/m

Grid 1 134.9 M2	Grid 2 139.3 M2	Grid 3 135.0 M2
Grid 4 93.7 M3	Grid 5 96.0 M3	Grid 6 91.5 M3
Grid 7 132.3 M2	Grid 8 138.1 M2	Grid 9 134.6 M2



0 dB = 139.3V/m

Figure 10 System Performance Check 1880MHz_E

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HAC_System Performance Check at 1880MHz_H

DUT: Dipole 1880 MHz; Type: CD1880V3; SN: 1115

Date/Time: 1/16/2012 10:08:22 AM

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to Dipole = 10mm/Hearing Aid

Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.462 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.489 A/m; Power Drift = 0.040 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.405 M2	Grid 2 0.419 M2	Grid 3 0.394 M2
Grid 4 0.448 M2	Grid 5 0.462 M2	Grid 6 0.435 M2
Grid 7 0.414 M2	Grid 8 0.427 M2	Grid 9 0.400 M2

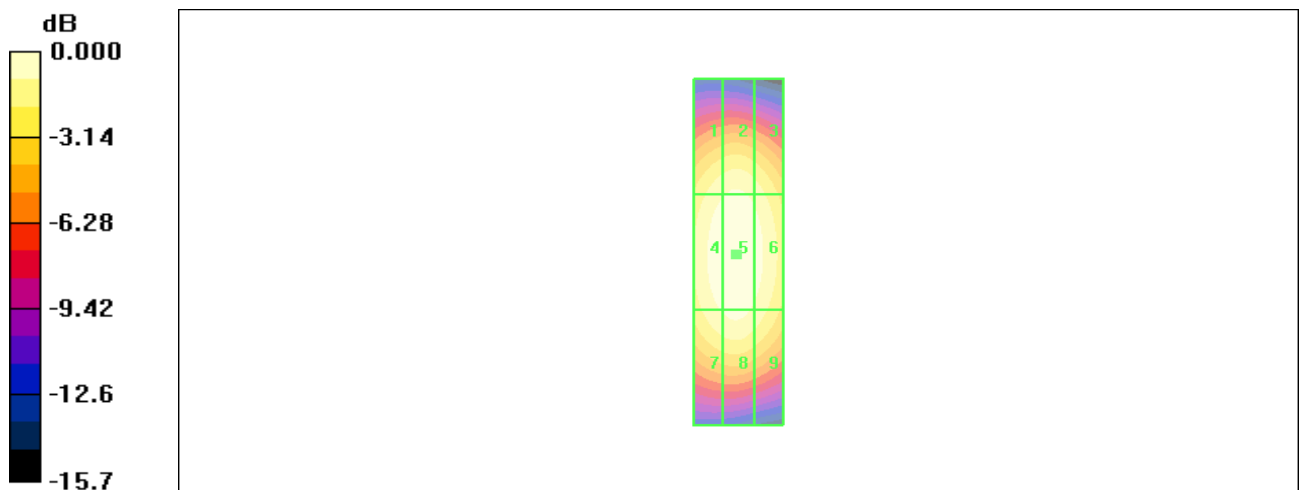


Figure 11 System Performance Check 1880MHz_H

ANNEX B: Graph Results

HAC RF E-Field GSM 850 High

Date/Time: 1/16/2012 3:34:18 PM

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 187.7 V/m

Probe Modulation Factor = 2.81

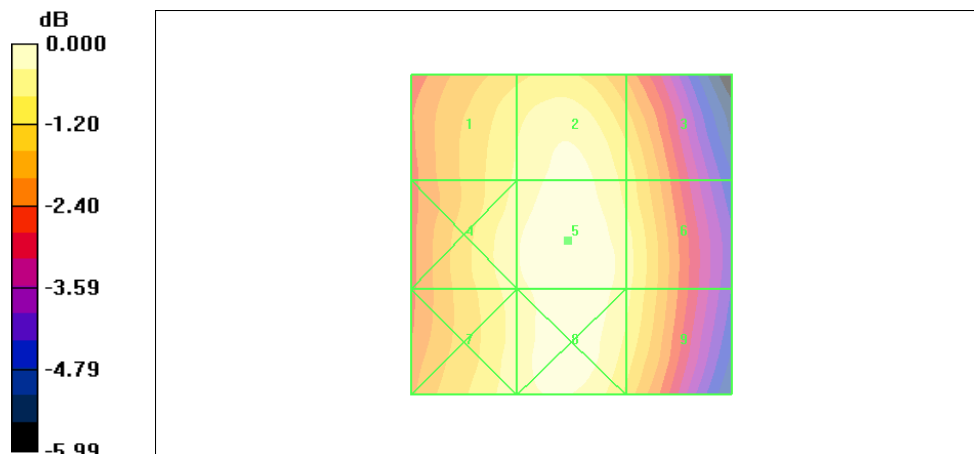
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 86.5 V/m; Power Drift = 0.055 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 172.9 M3	Grid 2 182.7 M3	Grid 3 168.5 M3
Grid 4 178.6 M3	Grid 5 187.7 M3	Grid 6 175.1 M3
Grid 7 176.0 M3	Grid 8 186.0 M3	Grid 9 173.8 M3



0 dB = 187.7V/m

Figure 12 HAC RF E-Field GSM 850 Channel 251

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HAC RF E-Field GSM 850 Middle

Date/Time: 1/16/2012 3:28:58 PM

Communication System: GSM 850; Frequency: 836.6 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 183.0 V/m

Probe Modulation Factor = 2.81

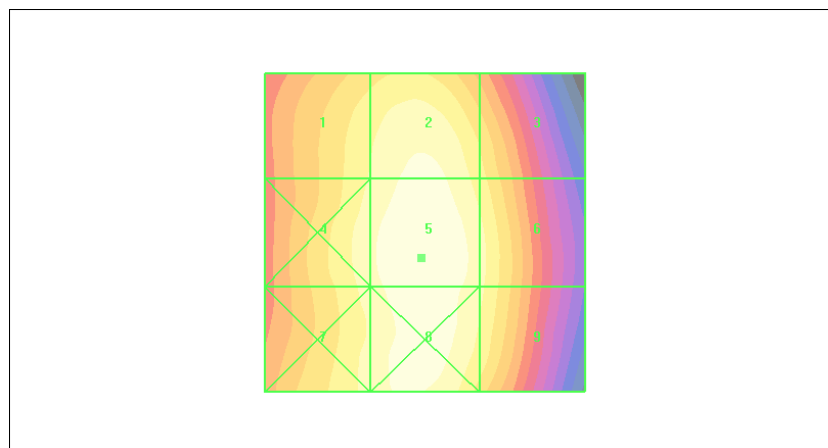
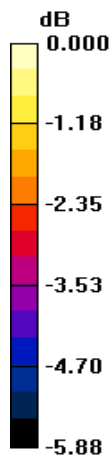
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 84.4 V/m; Power Drift = -0.032 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 168.1 M3	Grid 2 177.6 M3	Grid 3 163.4 M3
Grid 4 173.2 M3	Grid 5 183.0 M3	Grid 6 170.5 M3
Grid 7 171.2 M3	Grid 8 181.3 M3	Grid 9 169.3 M3



0 dB = 183.0V/m

Figure 13 HAC RF E-Field GSM 850 Channel 190

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HAC RF E-Field GSM 850 Low

Date/Time: 1/16/2012 3:39:28 PM

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 145.0 V/m

Probe Modulation Factor = 2.81

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 67.2 V/m; Power Drift = -0.115 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak E-field in V/m

Grid 1 133.7 M4	Grid 2 141.1 M4	Grid 3 130.6 M4
Grid 4 137.4 M4	Grid 5 145.0 M4	Grid 6 135.2 M4
Grid 7 134.9 M4	Grid 8 142.9 M4	Grid 9 134.0 M4

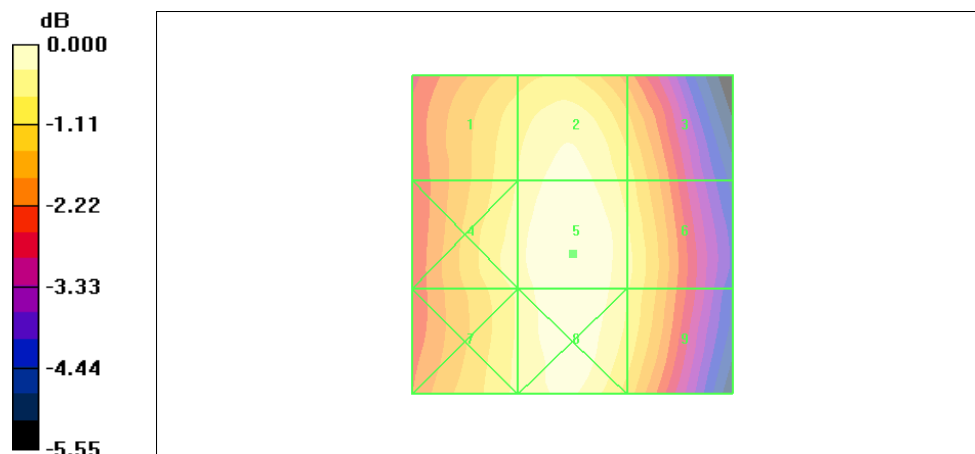


Figure 14 HAC RF E-Field GSM 850 Channel 128

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HAC RF H-Field GSM 850 High

Date/Time: 1/16/2012 7:36:40 PM

Communication System: GSM 850; Frequency: 848.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.251 A/m

Probe Modulation Factor = 2.75

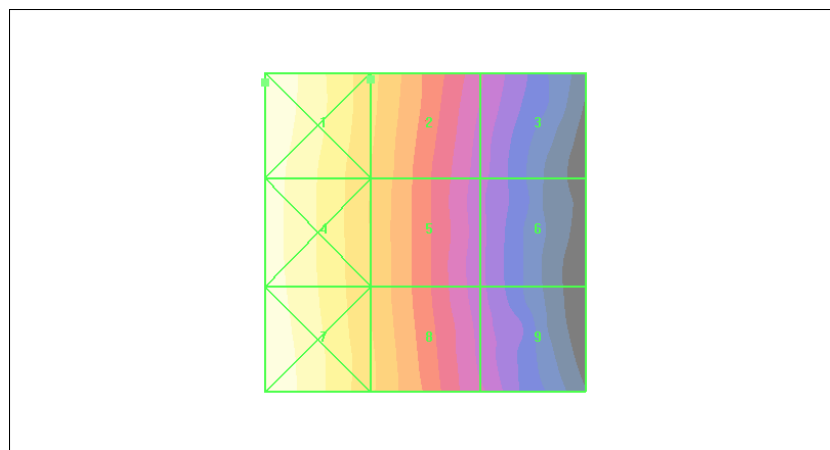
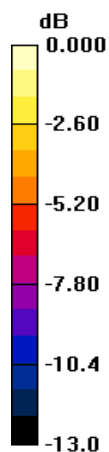
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.068 A/m; Power Drift = 0.030 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 0.363 M4	Grid 2 0.251 M4	Grid 3 0.151 M4
Grid 4 0.348 M4	Grid 5 0.243 M4	Grid 6 0.140 M4
Grid 7 0.360 M4	Grid 8 0.249 M4	Grid 9 0.152 M4



0 dB = 0.363A/m

Figure 15 HAC RF H-Field GSM 850Channel 251

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HAC RF H-Field GSM 850 Middle

Date/Time: 1/16/2012 7:31:45 PM

Communication System: GSM 850; Frequency: 836.6 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.209 A/m

Probe Modulation Factor = 2.75

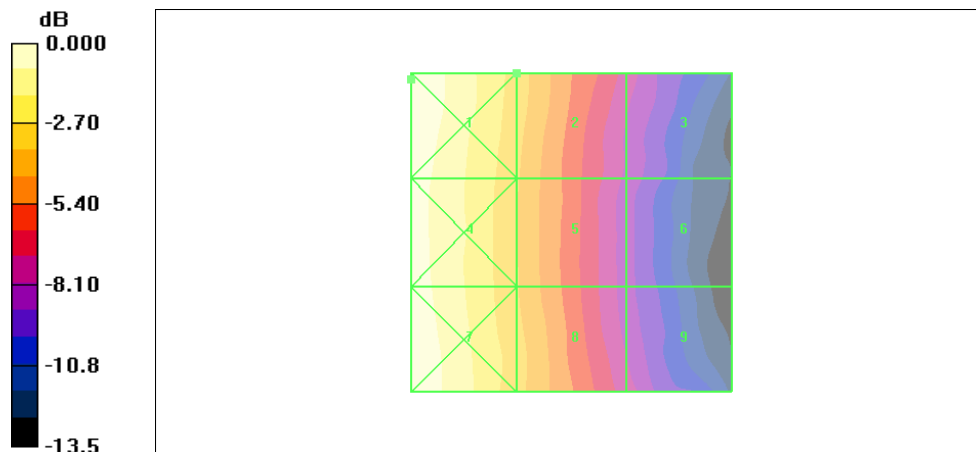
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.056 A/m; Power Drift = 0.136 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 0.300 M4	Grid 2 0.209 M4	Grid 3 0.126 M4
Grid 4 0.286 M4	Grid 5 0.201 M4	Grid 6 0.116 M4
Grid 7 0.297 M4	Grid 8 0.207 M4	Grid 9 0.125 M4



0 dB = 0.300A/m

Figure 16 HAC RF H-Field GSM 850 Channel 190

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HAC RF H-Field GSM 850 Low

Date/Time: 1/16/2012 7:41:42 PM

Communication System: GSM 850; Frequency: 824.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.157 A/m

Probe Modulation Factor = 2.75

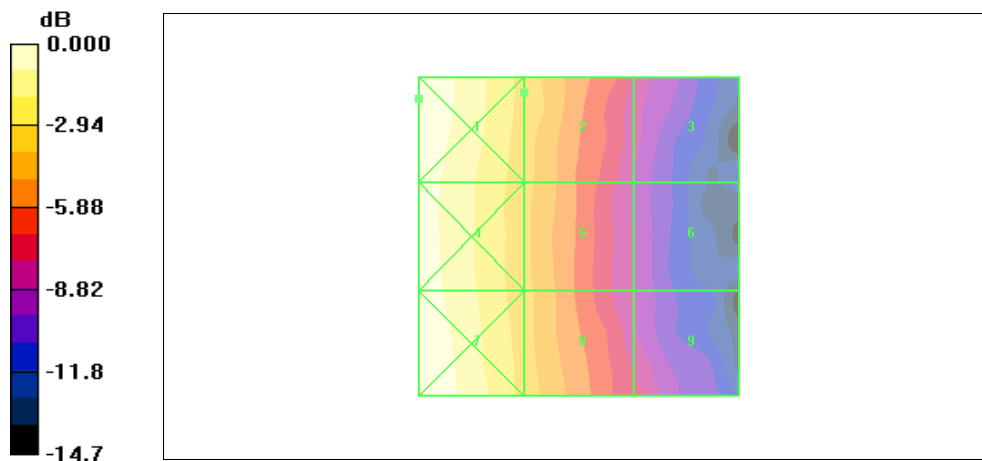
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.041 A/m; Power Drift = 0.169 dB

Hearing Aid Near-Field Category: M4 (AWF -5 dB)

Peak H-field in A/m

Grid 1 0.228 M4	Grid 2 0.157 M4	Grid 3 0.091 M4
Grid 4 0.218 M4	Grid 5 0.151 M4	Grid 6 0.083 M4
Grid 7 0.228 M4	Grid 8 0.156 M4	Grid 9 0.098 M4



0 dB = 0.228 A/m

Figure 17 HAC RF H-Field GSM 850 Channel 128

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HAC RF E-Field GSM 1900 High

Date/Time: 1/16/2012 3:49:35 PM

Communication System: PCS 1900; Frequency: 1909.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 69.2 V/m

Probe Modulation Factor = 2.84

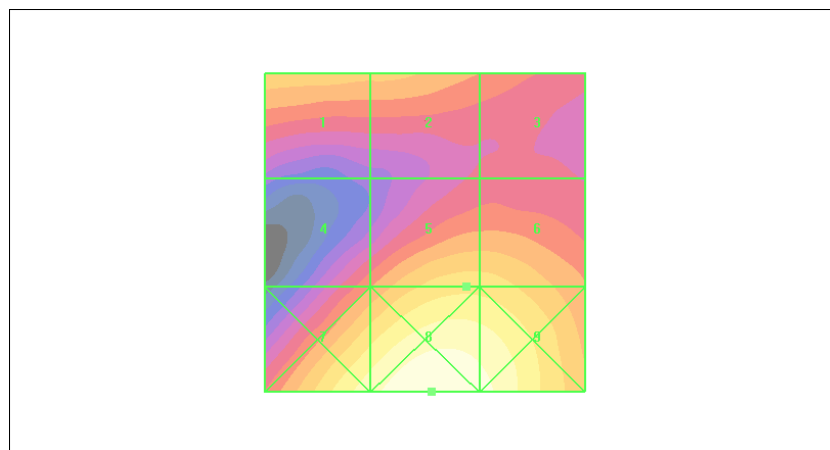
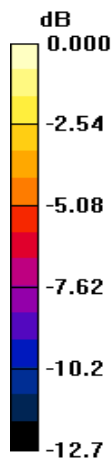
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 20.1 V/m; Power Drift = -0.080 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 62.9 M3	Grid 2 61.0 M3	Grid 3 53.4 M3
Grid 4 53.1 M3	Grid 5 69.2 M3	Grid 6 68.9 M3
Grid 7 84.1 M2	Grid 8 95.4 M2	Grid 9 90.0 M2



0 dB = 95.4V/m

Figure 18 HAC RF E-Field GSM 1900 Channel 810

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HAC RF E-Field GSM 1900 Middle

Date/Time: 1/16/2012 3:44:23 PM

Communication System: PCS 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 66.0 V/m

Probe Modulation Factor = 2.84

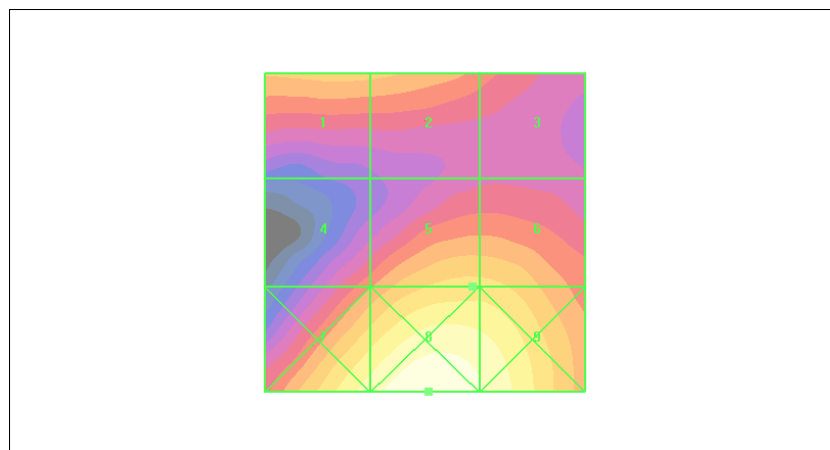
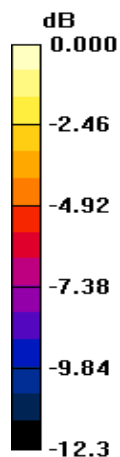
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.5 V/m; Power Drift = -0.040 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 60.3 M3	Grid 2 59.7 M3	Grid 3 50.2 M3
Grid 4 52.2 M3	Grid 5 66.0 M3	Grid 6 66.0 M3
Grid 7 81.0 M3	Grid 8 92.4 M2	Grid 9 85.2 M2



0 dB = 92.4V/m

Figure 19 HAC RF E-Field GSM 1900 Channel 661

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HAC RF E-Field GSM 1900 Low

Date/Time: 1/16/2012 3:54:44 PM

Communication System: PCS 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 66.2 V/m

Probe Modulation Factor = 2.84

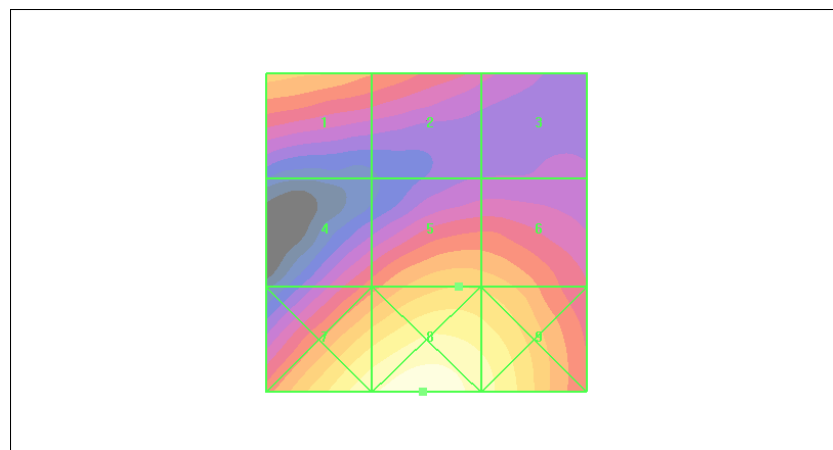
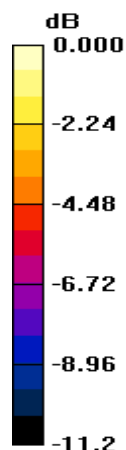
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 19.9 V/m; Power Drift = 0.057 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak E-field in V/m

Grid 1 63.3 M3	Grid 2 56.5 M3	Grid 3 45.1 M4
Grid 4 54.0 M3	Grid 5 66.2 M3	Grid 6 65.3 M3
Grid 7 85.1 M2	Grid 8 93.5 M2	Grid 9 82.6 M3



0 dB = 93.5V/m

Figure 20 HAC RF E-Field GSM 1900 Channel 512

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HAC RF H-Field GSM 1900 High

Date/Time: 1/16/2012 7:18:27 PM

Communication System: PCS 1900; Frequency: 1909.8 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.208 A/m

Probe Modulation Factor = 2.84

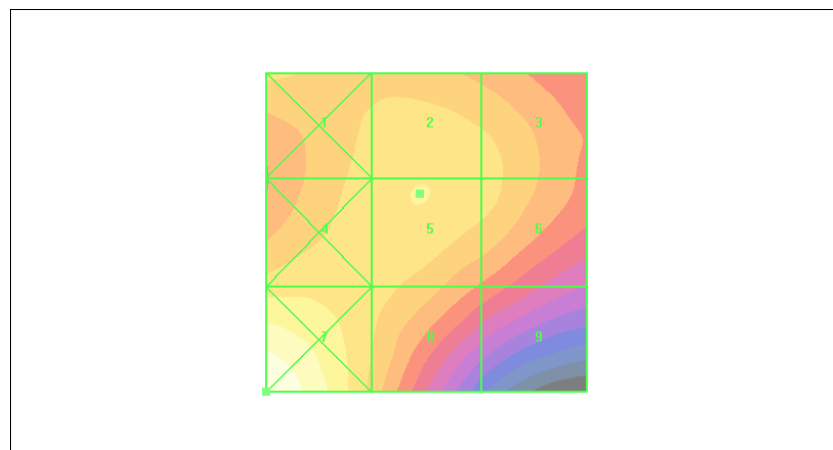
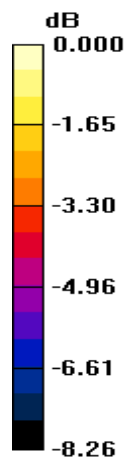
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.081 A/m; Power Drift = -0.012 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 0.201 M3	Grid 2 0.207 M3	Grid 3 0.201 M3
Grid 4 0.204 M3	Grid 5 0.208 M3	Grid 6 0.201 M3
Grid 7 0.251 M2	Grid 8 0.199 M3	Grid 9 0.170 M3



0 dB = 0.251 A/m

Figure 21 HAC RF H-Field GSM 1900 Channel 810

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HAC RF H-Field GSM 1900 Middle

Date/Time: 1/16/2012 7:13:09 PM

Communication System: PCS 1900; Frequency: 1880 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.192 A/m

Probe Modulation Factor = 2.84

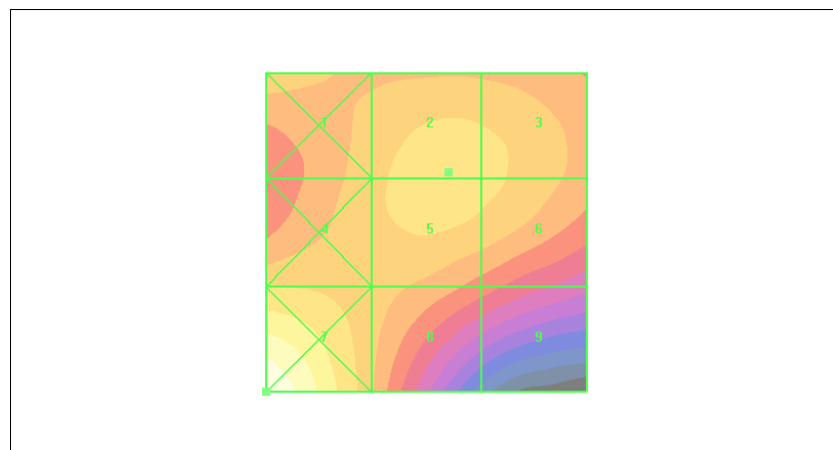
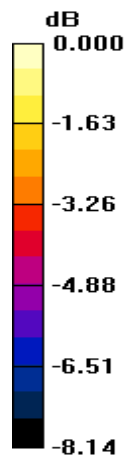
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.074 A/m; Power Drift = 0.035 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 0.183 M3	Grid 2 0.192 M3	Grid 3 0.189 M3
Grid 4 0.184 M3	Grid 5 0.192 M3	Grid 6 0.189 M3
Grid 7 0.237 M3	Grid 8 0.179 M3	Grid 9 0.158 M3



0 dB = 0.237 A/m

Figure 22 HAC RF H-Field GSM 1900 Channel 661

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HAC RF H-Field GSM 1900 Low

Date/Time: 1/16/2012 7:23:32 PM

Communication System: PCS 1900; Frequency: 1850.2 MHz; Duty Cycle: 1:8.3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.201 A/m

Probe Modulation Factor = 2.84

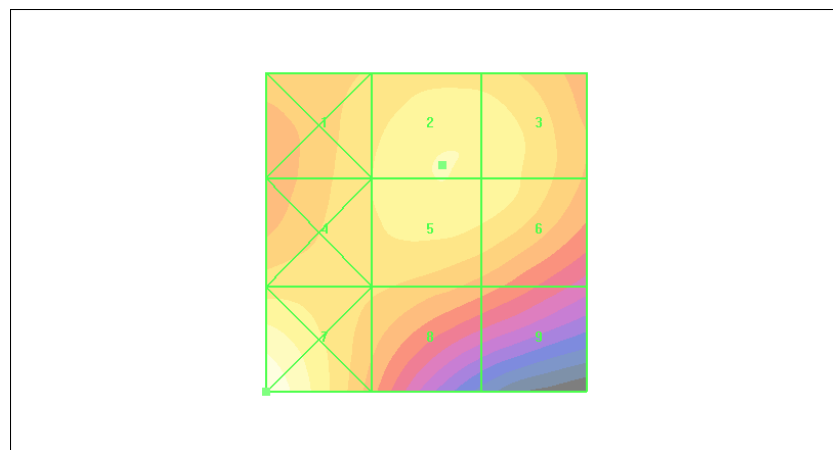
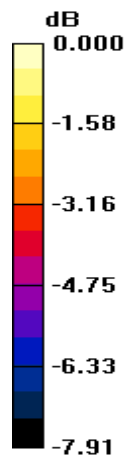
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.077 A/m; Power Drift = 0.038 dB

Hearing Aid Near-Field Category: M3 (AWF -5 dB)

Peak H-field in A/m

Grid 1 0.188 M3	Grid 2 0.201 M3	Grid 3 0.200 M3
Grid 4 0.189 M3	Grid 5 0.200 M3	Grid 6 0.199 M3
Grid 7 0.226 M3	Grid 8 0.179 M3	Grid 9 0.162 M3



0 dB = 0.226 A/m

Figure 23 HAC RF H-Field GSM 1900 Channel 512

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HAC RF E-Field WCDMA Band II High

Date/Time: 1/16/2012 4:32:38 PM

Communication System: WCDMA Band II; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 32.3 V/m

Probe Modulation Factor = 1.02

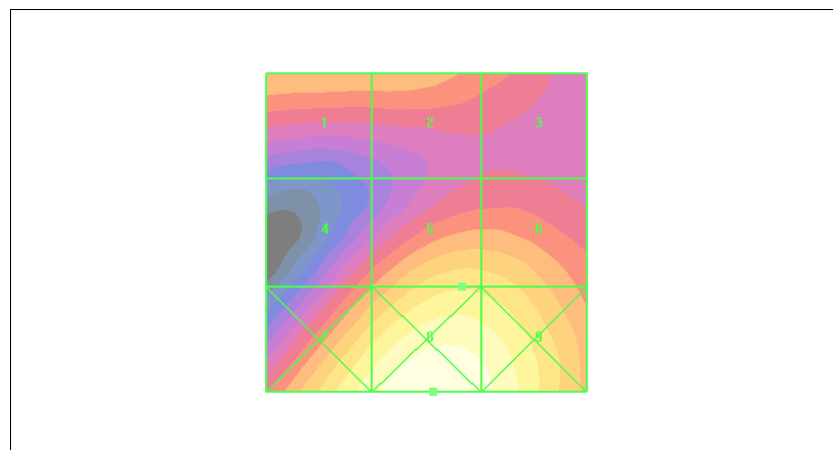
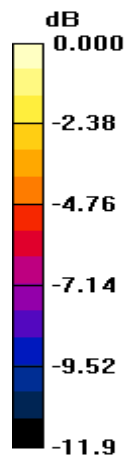
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 27.1 V/m; Power Drift = -0.007 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 27.4 M4	Grid 2 27.1 M4	Grid 3 24.1 M4
Grid 4 24.9 M4	Grid 5 32.3 M4	Grid 6 31.9 M4
Grid 7 38.3 M4	Grid 8 42.9 M4	Grid 9 40.4 M4



0 dB = 42.9V/m

Figure 24 HAC RF E-Field WCDMA Band II Channel 9538

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HAC RF E-Field WCDMA Band II Middle

Date/Time: 1/16/2012 4:27:31 PM

Communication System: WCDMA Band II; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 33.5 V/m

Probe Modulation Factor = 1.02

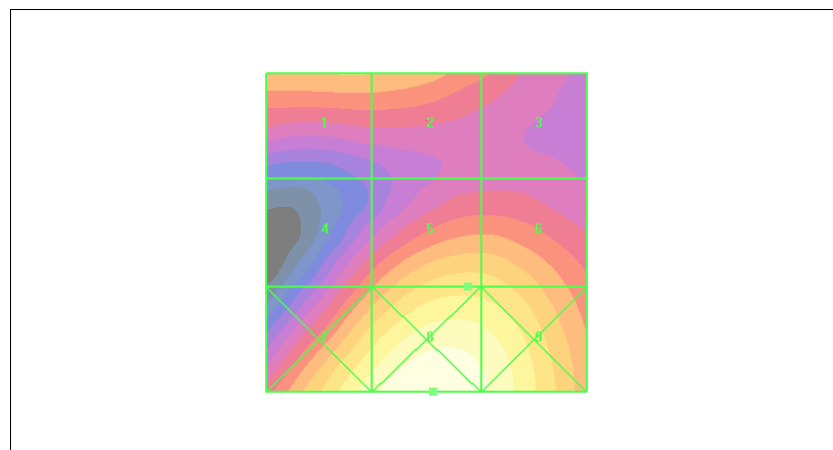
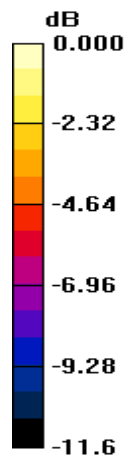
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 28.2 V/m; Power Drift = -0.005 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 29.3 M4	Grid 2 29.1 M4	Grid 3 24.8 M4
Grid 4 26.3 M4	Grid 5 33.5 M4	Grid 6 33.2 M4
Grid 7 40.1 M4	Grid 8 45.1 M4	Grid 9 42.2 M4



0 dB = 45.1V/m

Figure 25 HAC RF E-Field WCDMA Band II Channel 9400

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HAC RF E-Field WCDMA Band II Low

Date/Time: 1/16/2012 4:37:53 PM

Communication System: WCDMA Band II; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 34.6 V/m

Probe Modulation Factor = 1.02

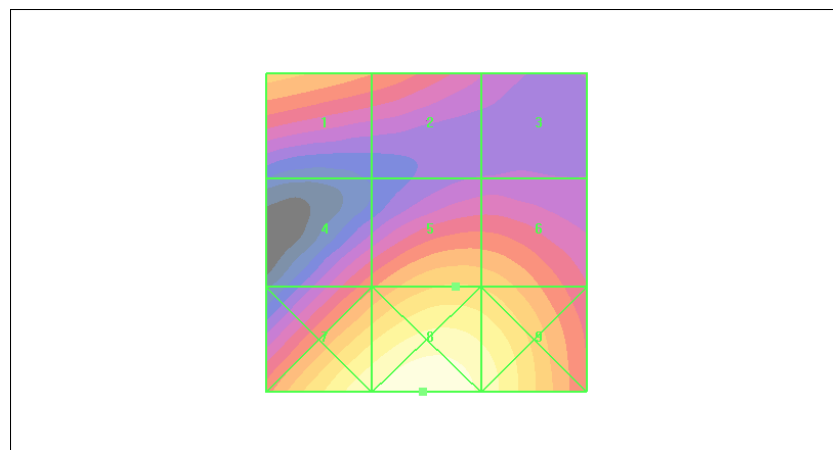
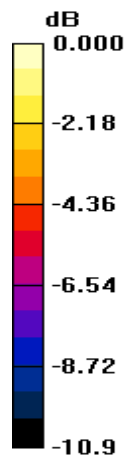
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 29.4 V/m; Power Drift = 0.033 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 32.7 M4	Grid 2 29.2 M4	Grid 3 22.8 M4
Grid 4 28.6 M4	Grid 5 34.6 M4	Grid 6 34.1 M4
Grid 7 44.2 M4	Grid 8 47.8 M4	Grid 9 43.2 M4



0 dB = 47.8V/m

Figure 26 HAC RF E-Field WCDMA Band II Channel 9262

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HAC RF E-Field WCDMA Band II HSDPA High

Date/Time: 1/16/2012 6:12:14 PM

Communication System: WCDMA Band II + HSDPA(8); Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 33.6 V/m

Probe Modulation Factor = 1.02

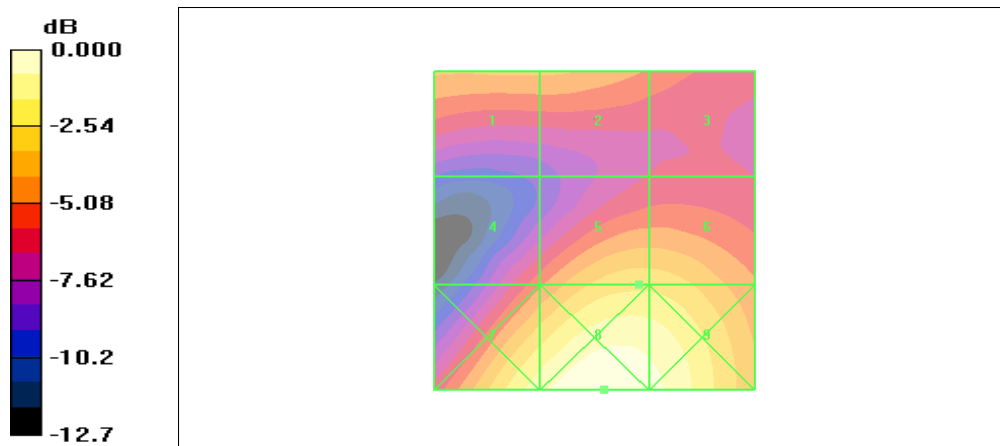
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 27.0 V/m; Power Drift = 0.099 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
29.0 M4	29.0 M4	25.5 M4
Grid 4	Grid 5	Grid 6
25.3 M4	33.6 M4	33.5 M4
Grid 7	Grid 8	Grid 9
40.5 M4	46.1 M4	43.4 M4



0 dB = 46.1V/m

Figure 27 HAC RF E-Field WCDMA Band II HSDPA Channel 9538

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HAC RF E-Field WCDMA Band II HSDPA Middle

Date/Time: 1/16/2012 6:07:03 PM

Communication System: WCDMA Band II + HSDPA(8); Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature:22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 35.6 V/m

Probe Modulation Factor = 1.02

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 29.4 V/m; Power Drift = -0.065 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
30.9 M4	30.8 M4	26.4 M4
Grid 4	Grid 5	Grid 6
27.2 M4	35.6 M4	35.4 M4
Grid 7	Grid 8	Grid 9
42.6 M4	48.2 M4	45.3 M4

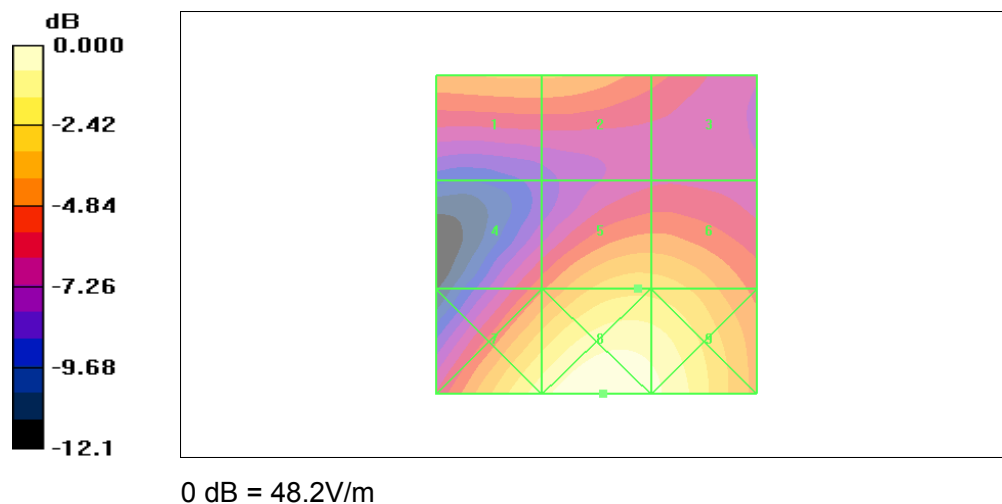


Figure 28 HAC RF E-Field WCDMA Band II HSDPA Channel 9400

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HAC RF E-Field WCDMA Band II HSDPA Low

Date/Time: 1/16/2012 6:17:16 PM

Communication System: WCDMA Band II + HSDPA(8); Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 36.8 V/m

Probe Modulation Factor = 1.02

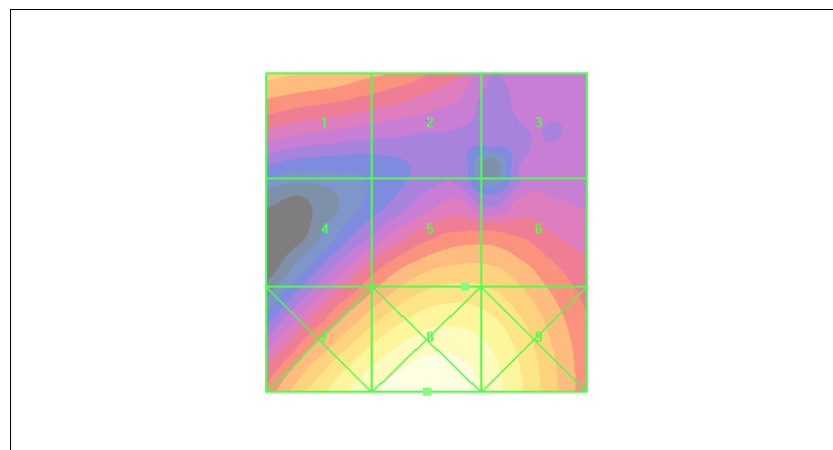
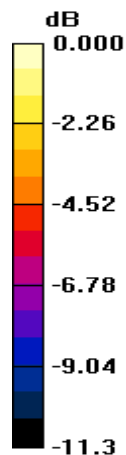
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 30.9 V/m; Power Drift = -0.027 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 34.1 M4	Grid 2 31.0 M4	Grid 3 22.7 M4
Grid 4 29.6 M4	Grid 5 36.8 M4	Grid 6 36.4 M4
Grid 7 46.6 M4	Grid 8 51.0 M4	Grid 9 46.6 M4



0 dB = 51.0V/m

Figure 29 HAC RF E-Field WCDMA Band II HSDPA Channel 9262

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HAC RF H-Field WCDMA Band II High

Date/Time: 1/16/2012 8:10:49 PM

Communication System: WCDMA Band II; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.097 A/m

Probe Modulation Factor = 1.01

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.105 A/m; Power Drift = -0.046 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.094 M4	Grid 2 0.097 M4	Grid 3 0.094 M4
Grid 4 0.093 M4	Grid 5 0.097 M4	Grid 6 0.094 M4
Grid 7 0.116 M4	Grid 8 0.091 M4	Grid 9 0.080 M4

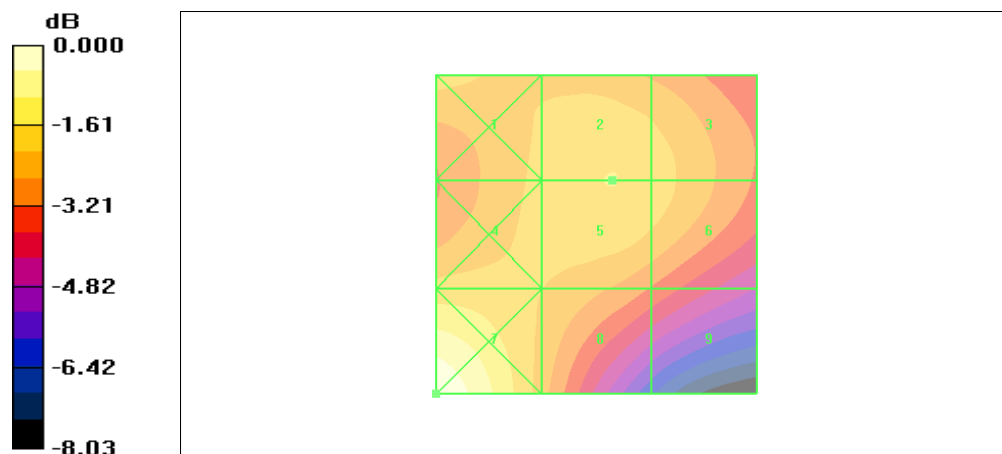


Figure 30 HAC RF H-Field WCDMA Band II Channel 9538

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HAC RF H-Field WCDMA Band II Middle

Date/Time: 1/16/2012 8:05:56 PM

Communication System: WCDMA Band II; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.098 A/m

Probe Modulation Factor = 1.01

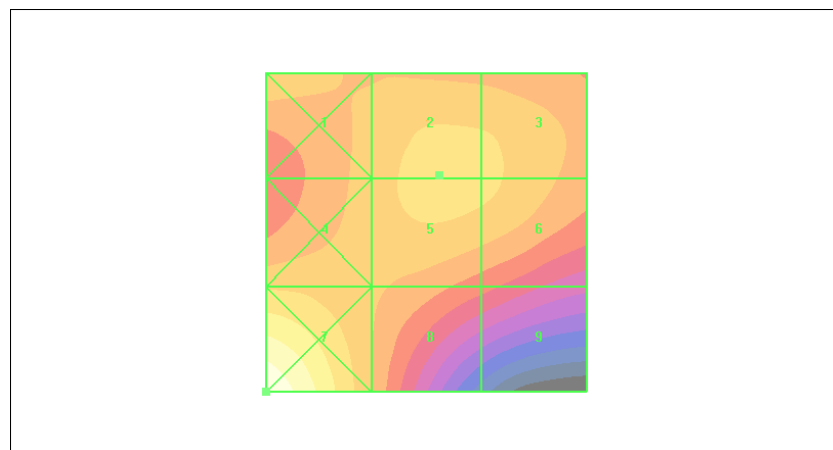
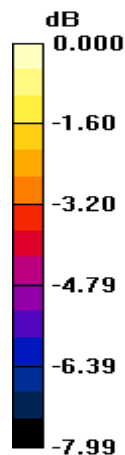
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.107 A/m; Power Drift = 0.007 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.095 M4	Grid 2 0.098 M4	Grid 3 0.097 M4
Grid 4 0.095 M4	Grid 5 0.098 M4	Grid 6 0.097 M4
Grid 7 0.122 M4	Grid 8 0.091 M4	Grid 9 0.081 M4



0 dB = 0.122A/m

Figure 31 HAC RF H-Field WCDMA Band II Channel 9400

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HAC RF H-Field WCDMA Band II Low

Date/Time: 1/16/2012 8:15:38 PM

Communication System: WCDMA Band II; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility

Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.110 A/m

Probe Modulation Factor = 1.01

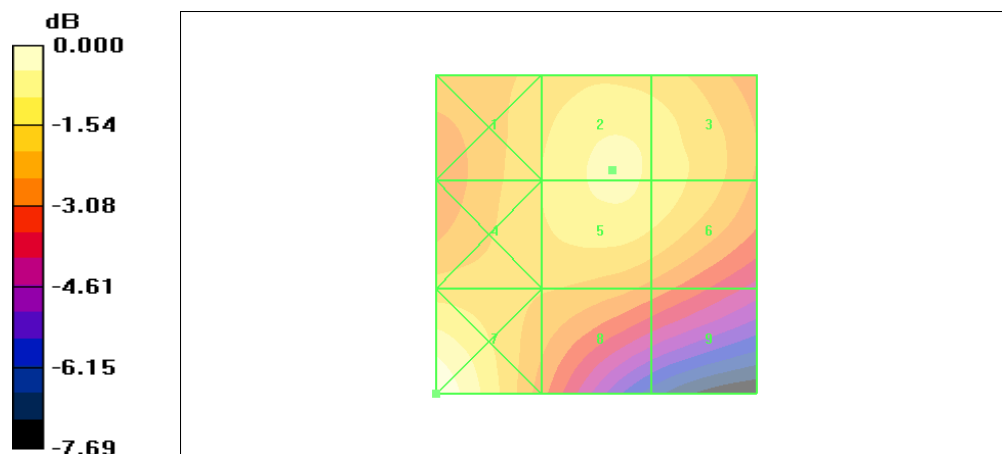
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.117 A/m; Power Drift = 0.040 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.102 M4	Grid 2 0.110 M4	Grid 3 0.108 M4
Grid 4 0.102 M4	Grid 5 0.110 M4	Grid 6 0.107 M4
Grid 7 0.122 M4	Grid 8 0.097 M4	Grid 9 0.089 M4



0 dB = 0.122A/m

Figure 32 HAC RF H-Field WCDMA Band II Channel 9262

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HAC RF H-Field WCDMA Band II HSDPA High

Date/Time: 1/16/2012 10:04:42 PM

Communication System: WCDMA Band II + HSDPA(8); Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.096 A/m

Probe Modulation Factor = 1.01

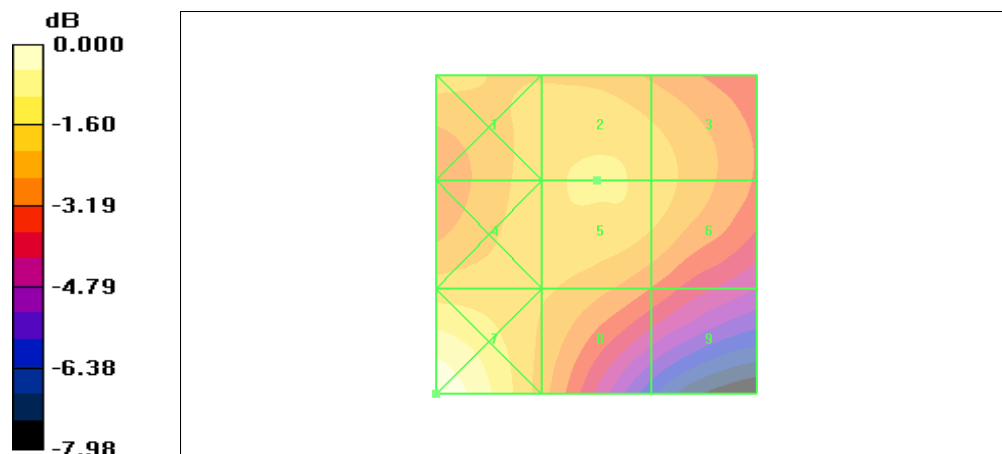
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.105 A/m; Power Drift = 0.042 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.093 M4	Grid 2 0.096 M4	Grid 3 0.094 M4
Grid 4 0.094 M4	Grid 5 0.096 M4	Grid 6 0.094 M4
Grid 7 0.115 M4	Grid 8 0.091 M4	Grid 9 0.080 M4



0 dB = 0.115A/m

Figure 33 HAC RF H-Field WCDMA Band II HSDPA Channel 9538

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HAC RF H-Field WCDMA Band II HSDPA Middle

Date/Time: 1/16/2012 9:59:55 PM

Communication System: WCDMA Band II + HSDPA(8); Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature:22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.097 A/m

Probe Modulation Factor = 1.01

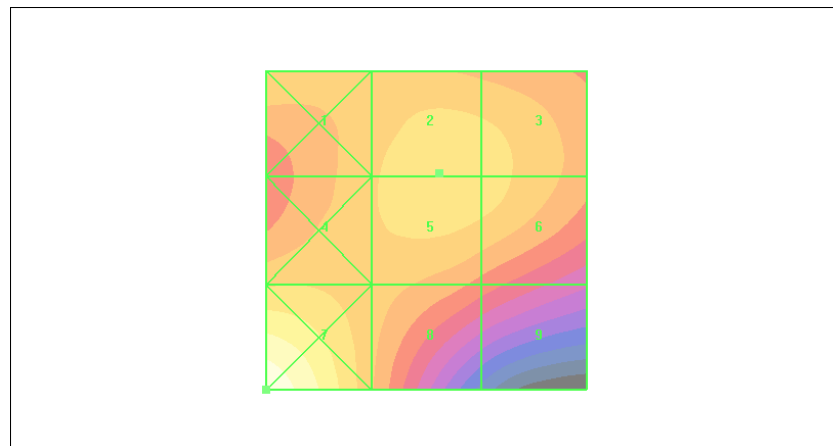
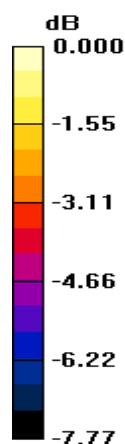
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.104 A/m; Power Drift = 0.160 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.094 M4	Grid 2 0.097 M4	Grid 3 0.096 M4
Grid 4 0.093 M4	Grid 5 0.097 M4	Grid 6 0.096 M4
Grid 7 0.118 M4	Grid 8 0.090 M4	Grid 9 0.081 M4



0 dB = 0.118A/m

Figure 34 HAC RF H-Field WCDMA Band II HSDPA Channel 9400

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HAC RF H-Field WCDMA Band II HSDPA Low

Date/Time: 1/16/2012 10:09:33 PM

Communication System: WCDMA Band II + HSDPA(8); Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility

Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.109 A/m

Probe Modulation Factor = 1.01

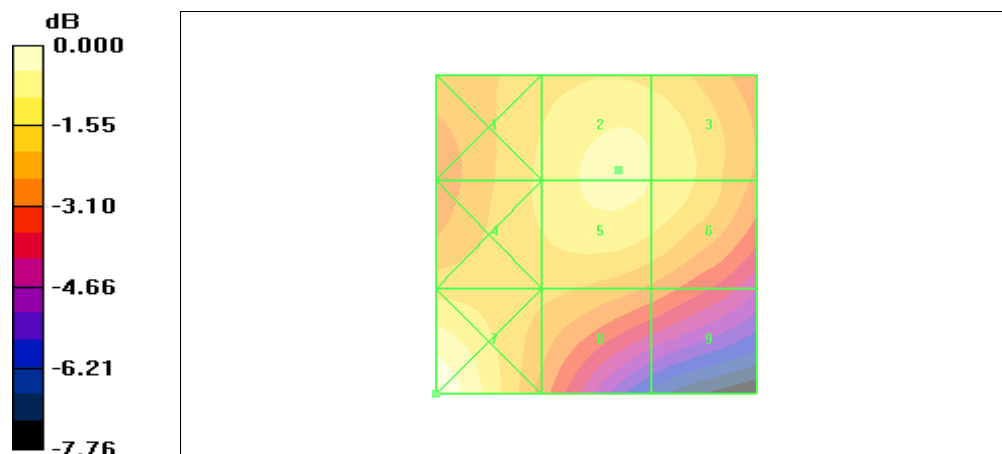
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.117 A/m; Power Drift = 0.032 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.103 M4	Grid 2 0.109 M4	Grid 3 0.107 M4
Grid 4 0.103 M4	Grid 5 0.109 M4	Grid 6 0.107 M4
Grid 7 0.121 M4	Grid 8 0.097 M4	Grid 9 0.089 M4



0 dB = 0.121 A/m

Figure 35 HAC RF H-Field WCDMA Band II HSDPA Channel 9262

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HAC RF E-Field WCDMA Band IV High

Date/Time: 1/16/2012 5:00:35 PM

Communication System: WCDMA Band IV; Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 40.9 V/m

Probe Modulation Factor = 1.02

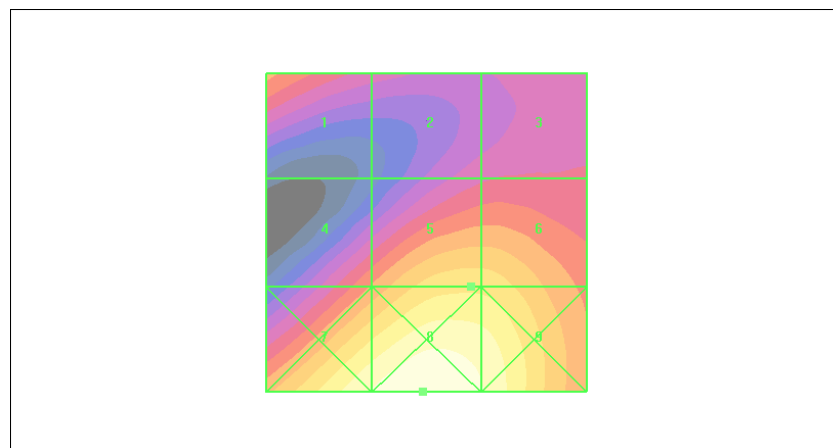
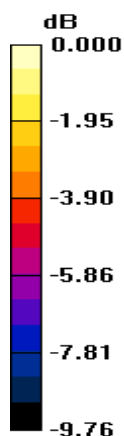
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 37.6 V/m; Power Drift = 0.027 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 34.2 M4	Grid 2 28.2 M4	Grid 3 28.9 M4
Grid 4 33.6 M4	Grid 5 40.9 M4	Grid 6 40.7 M4
Grid 7 48.6 M4	Grid 8 52.0 M4	Grid 9 48.6 M4



0 dB = 52.0V/m

Figure 36 HAC RF E-Field WCDMA Band IV Channel 1513

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HAC RF E-Field WCDMA Band IV Middle

Date/Time: 1/16/2012 4:55:33 PM

Communication System: WCDMA Band IV; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 37.7 V/m

Probe Modulation Factor = 1.02

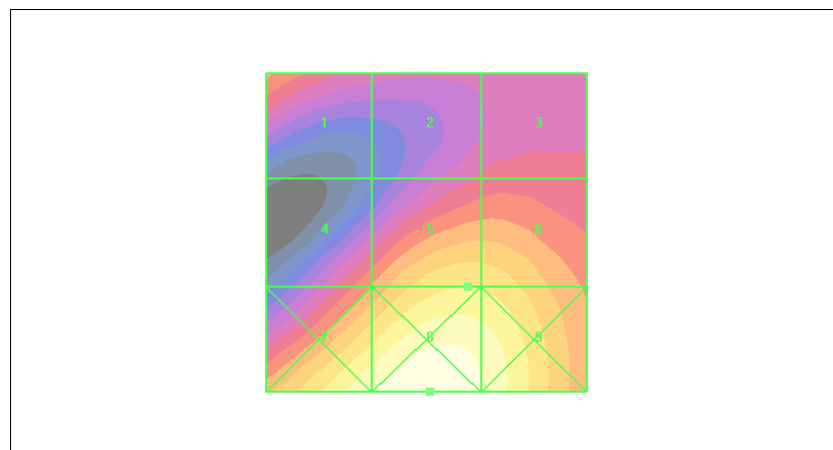
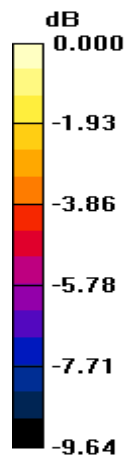
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 35.2 V/m; Power Drift = 0.014 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
30.9 M4	26.5 M4	27.2 M4
Grid 4	Grid 5	Grid 6
30.5 M4	37.7 M4	37.5 M4
Grid 7	Grid 8	Grid 9
43.8 M4	47.1 M4	44.0 M4



0 dB = 47.1V/m

Figure 37 HAC RF E-Field WCDMA Band IV Channel 1413

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HAC RF E-Field WCDMA Band IV Low

Date/Time: 1/16/2012 5:07:14 PM

Communication System: WCDMA Band IV; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 40.3 V/m

Probe Modulation Factor = 1.02

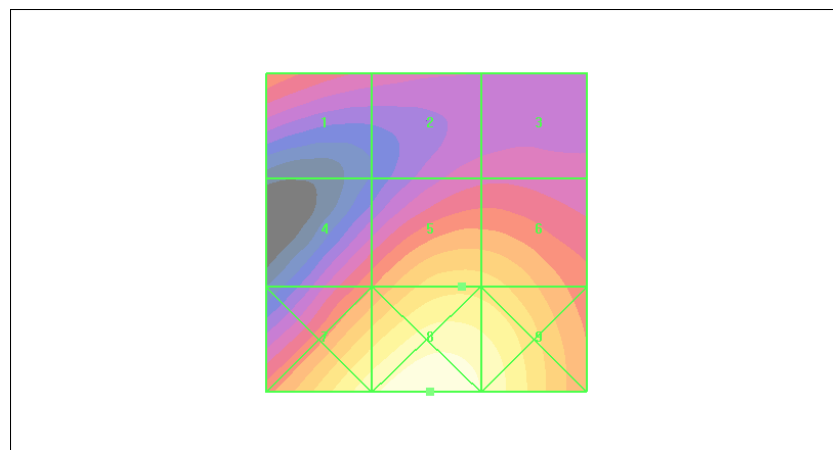
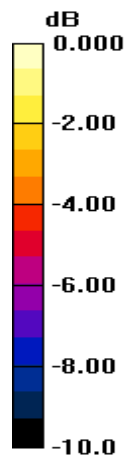
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 37.4 V/m; Power Drift = 0.016 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 32.4 M4	Grid 2 27.6 M4	Grid 3 27.7 M4
Grid 4 32.6 M4	Grid 5 40.3 M4	Grid 6 39.8 M4
Grid 7 47.2 M4	Grid 8 51.8 M4	Grid 9 48.0 M4



0 dB = 51.8V/m

Figure 38 HAC RF E-Field WCDMA Band IV Channel 1312

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HAC RF E-Field WCDMA Band IV HSDPA High

Date/Time: 1/16/2012 5:56:03 PM

Communication System: WCDMA Band IV + HSDPA(8); Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 41.3 V/m

Probe Modulation Factor = 1.02

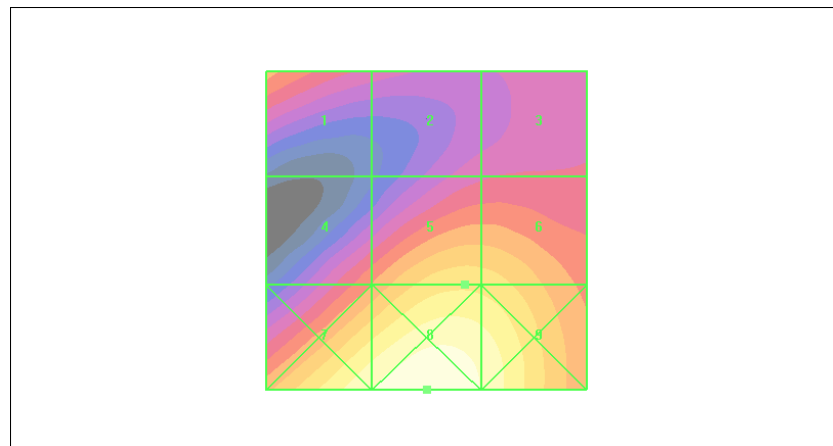
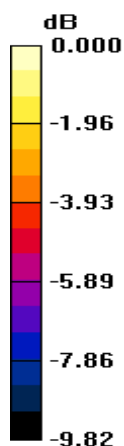
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 37.8 V/m; Power Drift = 0.038 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 34.6 M4	Grid 2 28.4 M4	Grid 3 29.1 M4
Grid 4 33.7 M4	Grid 5 41.3 M4	Grid 6 40.9 M4
Grid 7 49.0 M4	Grid 8 52.6 M4	Grid 9 48.7 M4



0 dB = 52.6V/m

Figure 39 HAC RF E-Field WCDMA Band IV HSDPA Channel 1513

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HAC RF E-Field WCDMA Band IV HSDPA Middle

Date/Time: 1/16/2012 5:50:59 PM

Communication System: WCDMA Band IV + HSDPA(8); Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 38.0 V/m

Probe Modulation Factor = 1.02

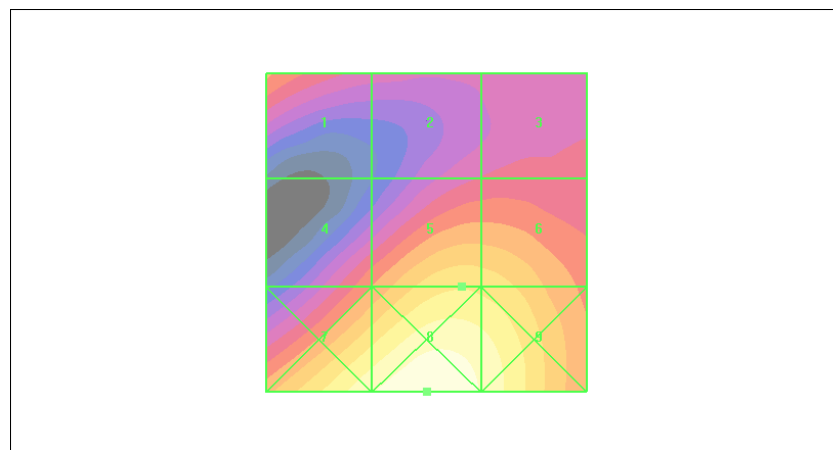
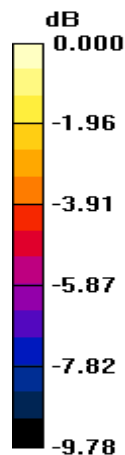
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 35.1 V/m; Power Drift = 0.059 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 31.3 M4	Grid 2 26.5 M4	Grid 3 27.2 M4
Grid 4 30.6 M4	Grid 5 38.0 M4	Grid 6 37.5 M4
Grid 7 44.2 M4	Grid 8 47.9 M4	Grid 9 44.2 M4



0 dB = 47.9V/m

Figure 40 HAC RF E-Field WCDMA Band IV HSDPA Channel 1413

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HAC RF E-Field WCDMA Band IV HSDPA Low

Date/Time: 1/16/2012 6:01:24 PM

Communication System: WCDMA Band IV + HSDPA(8); Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 40.4 V/m

Probe Modulation Factor = 1.02

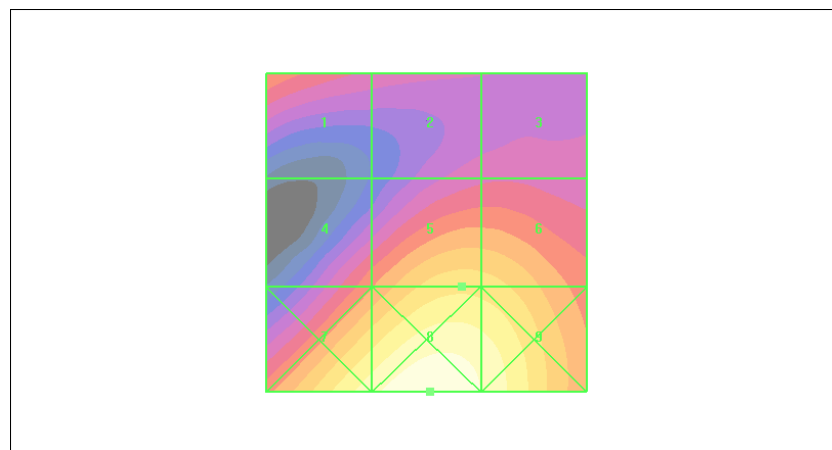
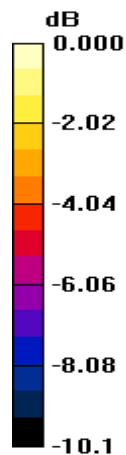
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 37.4 V/m; Power Drift = -0.021 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 32.5 M4	Grid 2 27.7 M4	Grid 3 27.9 M4
Grid 4 32.6 M4	Grid 5 40.4 M4	Grid 6 40.0 M4
Grid 7 47.2 M4	Grid 8 52.1 M4	Grid 9 48.2 M4



0 dB = 52.1V/m

Figure 41 HAC RF E-Field WCDMA Band IV HSDPA Channel 1312

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HAC RF H-Field WCDMA Band IV High

Date/Time: 1/16/2012 8:26:18 PM

Communication System: WCDMA Band IV; Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.114 A/m

Probe Modulation Factor = 1.01

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.115 A/m; Power Drift = 0.087 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.114 M4	Grid 2 0.114 M4	Grid 3 0.107 M4
Grid 4 0.113 M4	Grid 5 0.113 M4	Grid 6 0.106 M4
Grid 7 0.128 M4	Grid 8 0.104 M4	Grid 9 0.087 M4

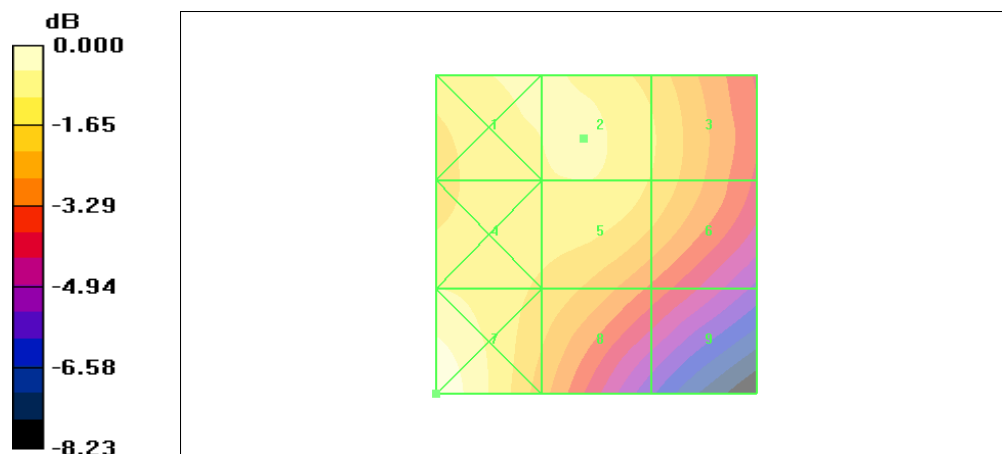


Figure 42 HAC RF H-Field WCDMA Band IV Channel 1513

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HAC RF H-Field WCDMA Band IV Middle

Date/Time: 1/16/2012 8:21:11 PM

Communication System: WCDMA Band IV; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.105 A/m

Probe Modulation Factor = 1.01

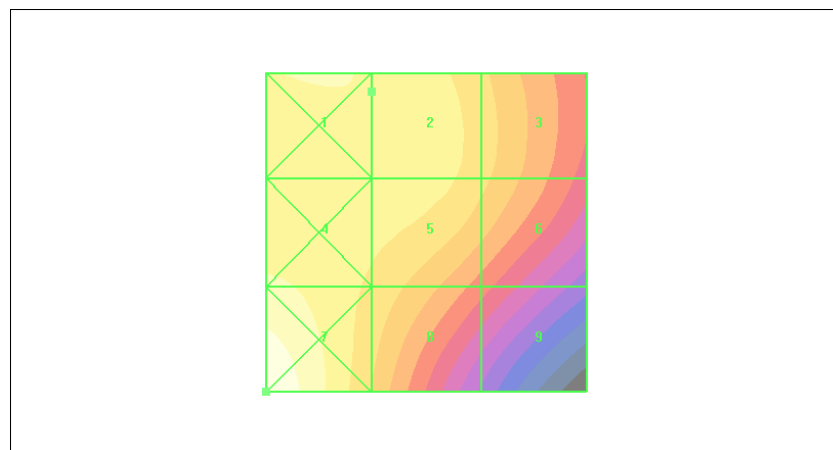
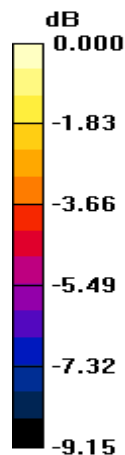
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.104 A/m; Power Drift = 0.009 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.106 M4	Grid 2 0.105 M4	Grid 3 0.095 M4
Grid 4 0.107 M4	Grid 5 0.102 M4	Grid 6 0.093 M4
Grid 7 0.121 M4	Grid 8 0.097 M4	Grid 9 0.077 M4



0 dB = 0.121 A/m

Figure 43 HAC RF H-Field WCDMA Band IV Channel 1413

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HAC RF H-Field WCDMA Band IV Low

Date/Time: 1/16/2012 8:31:20 PM

Communication System: WCDMA Band IV; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility

Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.110 A/m

Probe Modulation Factor = 1.01

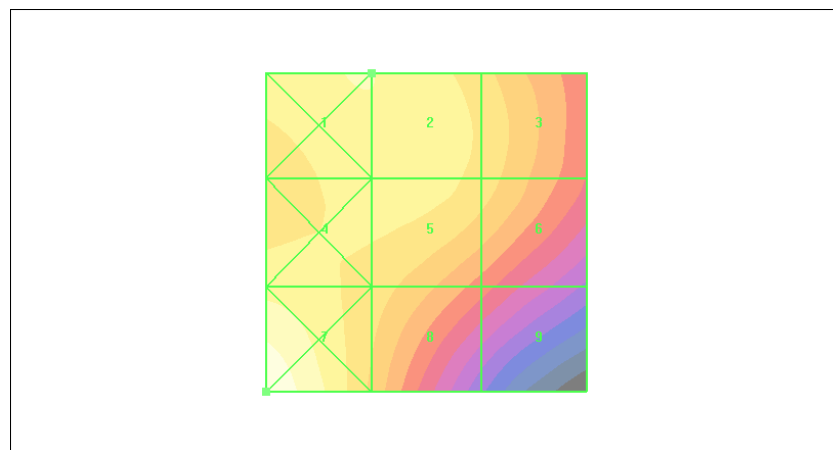
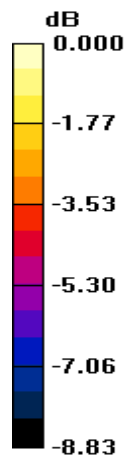
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.108 A/m; Power Drift = 0.088 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.111 M4	Grid 2 0.110 M4	Grid 3 0.102 M4
Grid 4 0.108 M4	Grid 5 0.107 M4	Grid 6 0.100 M4
Grid 7 0.126 M4	Grid 8 0.100 M4	Grid 9 0.081 M4



0 dB = 0.126 A/m

Figure 44 HAC RF H-Field WCDMA Band IV Channel 1312

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HAC RF H-Field WCDMA Band IV HSDPA High

Date/Time: 1/16/2012 10:19:32 PM

Communication System: WCDMA Band IV + HSDPA(8); Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.113 A/m

Probe Modulation Factor = 1.01

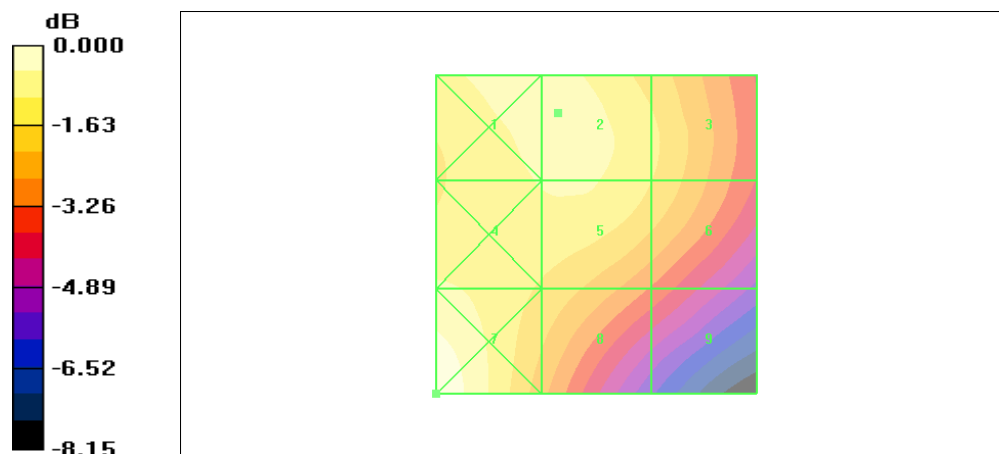
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.115 A/m; Power Drift = 0.052 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.113 M4	Grid 2 0.113 M4	Grid 3 0.105 M4
Grid 4 0.112 M4	Grid 5 0.111 M4	Grid 6 0.104 M4
Grid 7 0.125 M4	Grid 8 0.103 M4	Grid 9 0.085 M4



0 dB = 0.125 A/m

Figure 45 HAC RF H-Field WCDMA Band IV HSDPA Channel 1513

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HAC RF H-Field WCDMA Band IV HSDPA Middle

Date/Time: 1/16/2012 10:14:46 PM

Communication System: WCDMA Band IV + HSDPA(8); Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.104 A/m

Probe Modulation Factor = 1.01

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.104 A/m; Power Drift = 0.033 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.105 M4	Grid 2 0.104 M4	Grid 3 0.094 M4
Grid 4 0.105 M4	Grid 5 0.102 M4	Grid 6 0.093 M4
Grid 7 0.119 M4	Grid 8 0.096 M4	Grid 9 0.076 M4

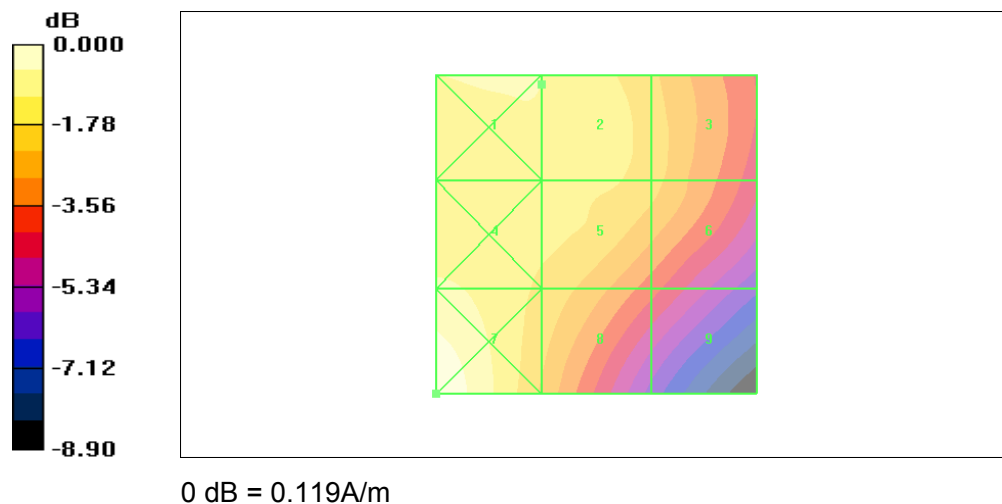


Figure 46 HAC RF H-Field WCDMA Band IV HSDPA Channel 1413

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HAC RF H-Field WCDMA Band IV HSDPA Low

Date/Time: 1/16/2012 10:24:28 PM

Communication System: WCDMA Band IV + HSDPA(8); Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.109 A/m

Probe Modulation Factor = 1.01

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.109 A/m; Power Drift = 0.052 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.111 M4	Grid 2 0.109 M4	Grid 3 0.101 M4
Grid 4 0.108 M4	Grid 5 0.107 M4	Grid 6 0.100 M4
Grid 7 0.125 M4	Grid 8 0.099 M4	Grid 9 0.081 M4

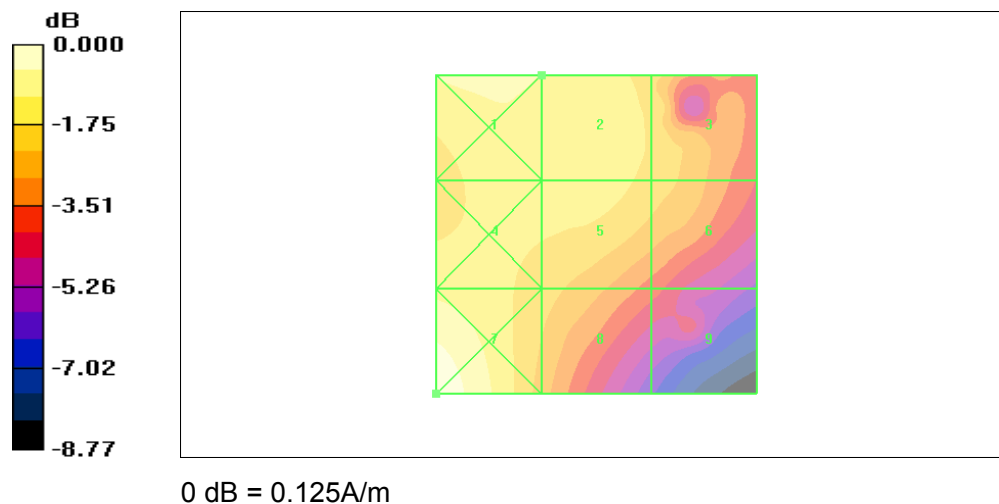


Figure 47 HAC RF H-Field WCDMA Band IV HSDPA Channel 1312

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HAC RF E-Field WCDMA Band V High

Date/Time: 1/16/2012 4:10:14 PM

Communication System: WCDMA Band V; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 65.3 V/m

Probe Modulation Factor = 1.03

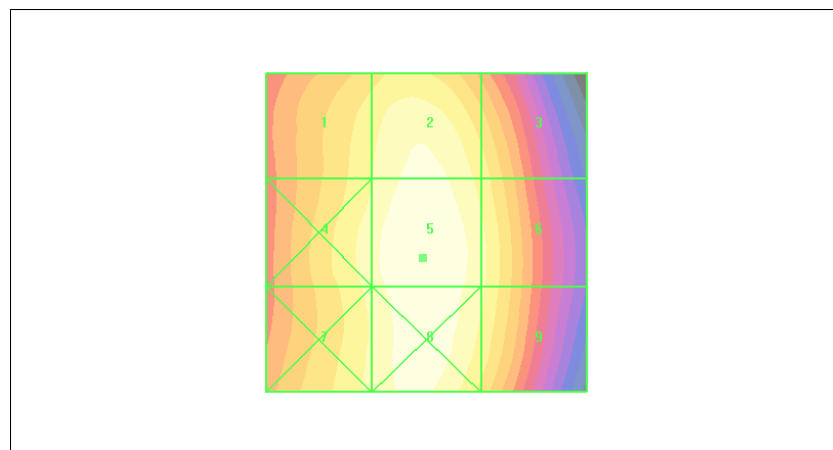
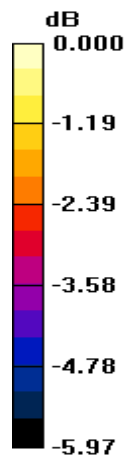
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 82.0 V/m; Power Drift = -0.078 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
59.6 M4	63.3 M4	58.5 M4
Grid 4	Grid 5	Grid 6
61.5 M4	65.3 M4	60.6 M4
Grid 7	Grid 8	Grid 9
60.7 M4	64.7 M4	60.2 M4



0 dB = 65.3V/m

Figure 48 HAC RF E-Field WCDMA Band V Channel 4233

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HAC RF E-Field WCDMA Band V Middle

Date/Time: 1/16/2012 4:05:05 PM

Communication System: WCDMA Band V; Frequency: 836.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 58.3 V/m

Probe Modulation Factor = 1.03

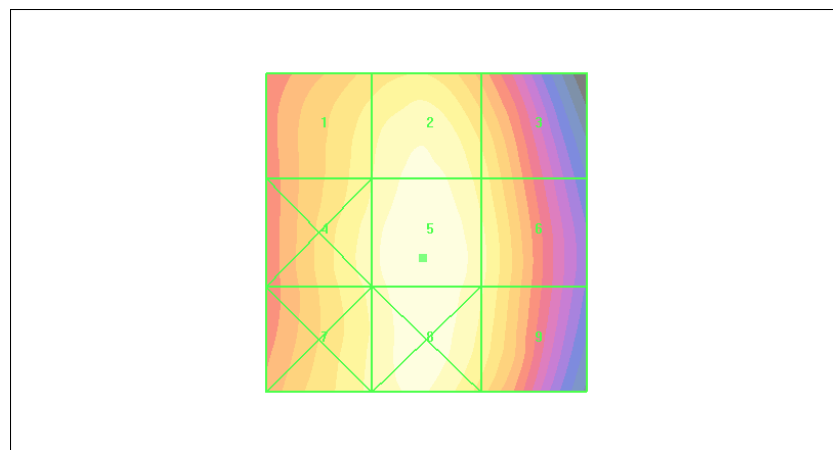
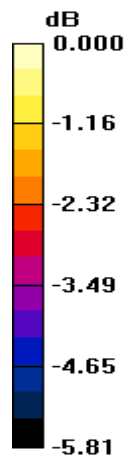
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 72.6 V/m; Power Drift = 0.074 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 53.3 M4	Grid 2 56.4 M4	Grid 3 52.3 M4
Grid 4 55.0 M4	Grid 5 58.3 M4	Grid 6 54.2 M4
Grid 7 54.3 M4	Grid 8 57.8 M4	Grid 9 53.7 M4



0 dB = 58.3V/m

Figure 49 HAC RF E-Field WCDMA Band V Channel 4183

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HAC RF E-Field WCDMA Band V Low

Date/Time: 1/16/2012 4:20:09 PM

Communication System: WCDMA Band V; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 59.4 V/m

Probe Modulation Factor = 1.03

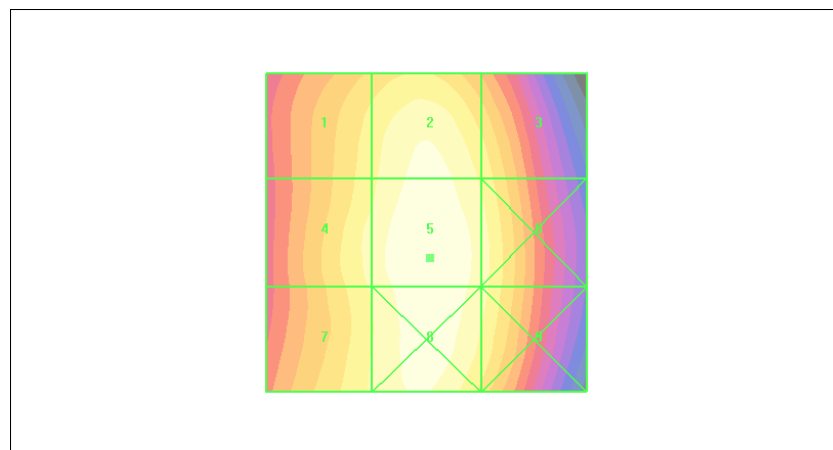
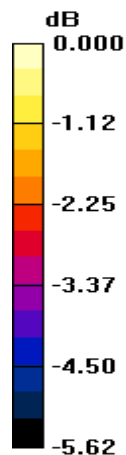
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 75.1 V/m; Power Drift = -0.033 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 53.9 M4	Grid 2 57.8 M4	Grid 3 54.1 M4
Grid 4 55.6 M4	Grid 5 59.4 M4	Grid 6 55.8 M4
Grid 7 54.9 M4	Grid 8 58.8 M4	Grid 9 55.5 M4



0 dB = 59.4V/m

Figure 50 HAC RF E-Field WCDMA Band V Channel 4132

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HAC RF E-Field WCDMA Band V HSDPA High

Date/Time: 1/16/2012 6:27:40 PM

Communication System: WCDMA Band V + HSDPA(8); Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device High/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 64.7 V/m

Probe Modulation Factor = 1.03

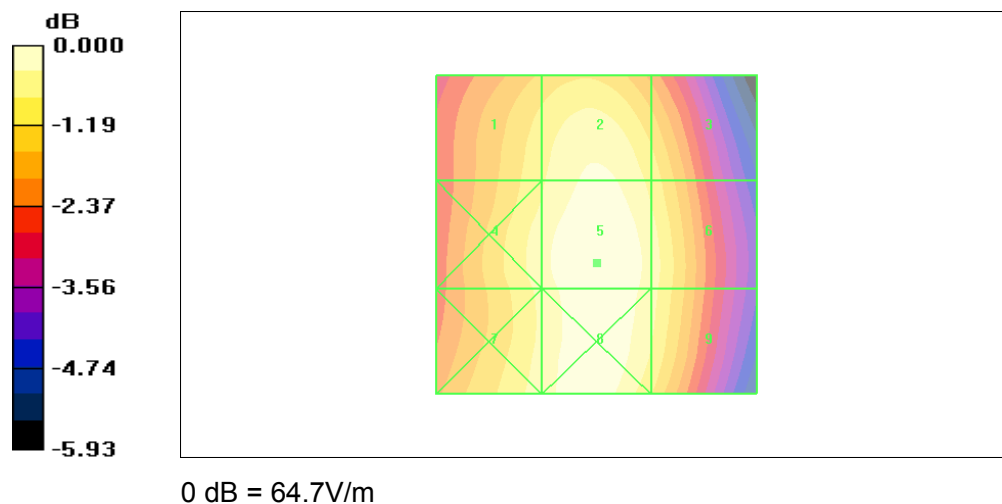
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 81.6 V/m; Power Drift = -0.060 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1 58.8 M4	Grid 2 62.4 M4	Grid 3 58.3 M4
Grid 4 60.9 M4	Grid 5 64.7 M4	Grid 6 60.7 M4
Grid 7 60.6 M4	Grid 8 64.2 M4	Grid 9 60.3 M4



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HAC RF E-Field WCDMA Band V HSDPA Middle

Date/Time: 1/16/2012 6:22:44 PM

Communication System: WCDMA Band V + HSDPA(8); Frequency: 836.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 58.3 V/m

Probe Modulation Factor = 1.03

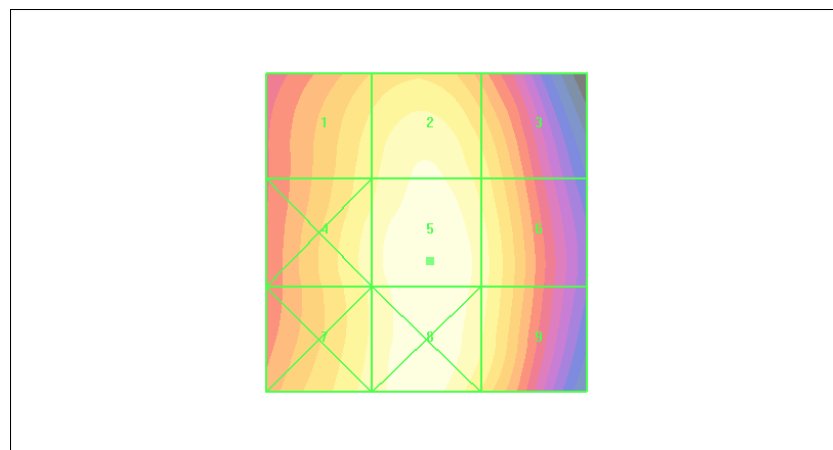
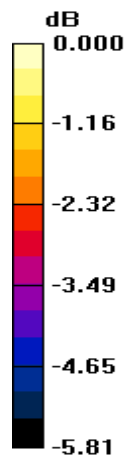
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 73.5 V/m; Power Drift = -0.056 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
52.8 M4	56.3 M4	52.4 M4
Grid 4	Grid 5	Grid 6
54.7 M4	58.3 M4	54.6 M4
Grid 7	Grid 8	Grid 9
54.6 M4	57.9 M4	54.4 M4



0 dB = 58.3V/m

Figure 52 HAC RF E-Field WCDMA Band V HSDPA Channel 4183

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HAC RF E-Field WCDMA Band V HSDPA Low

Date/Time: 1/16/2012 6:32:39 PM

Communication System: WCDMA Band V + HSDPA(8); Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: ER3DV6 - SN2302; ConvF (1, 1, 1); Calibrated: 06/15/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - ER3D - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 61.2 V/m

Probe Modulation Factor = 1.03

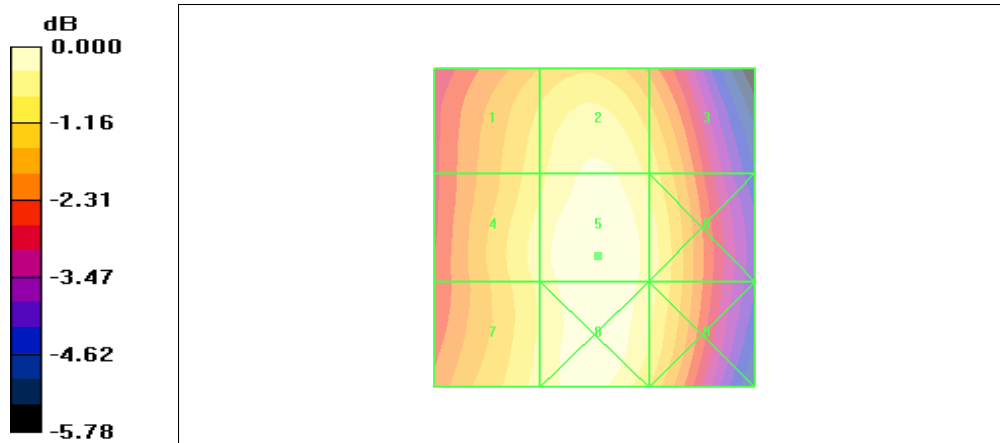
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 76.9 V/m; Power Drift = -0.007 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
55.4 M4	59.1 M4	55.3 M4
Grid 4	Grid 5	Grid 6
57.4 M4	61.2 M4	57.5 M4
Grid 7	Grid 8	Grid 9
57.0 M4	60.7 M4	57.3 M4



0 dB = 61.2V/m

Figure 53 HAC RF E-Field WCDMA Band V HSDPA Channel 4132

TA Technology (Shanghai) Co., Ltd.

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HAC RF H-Field WCDMA Band V High

Date/Time: 1/16/2012 8:42:07 PM

Communication System: WCDMA Band V; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.086 A/m

Probe Modulation Factor = 1.01

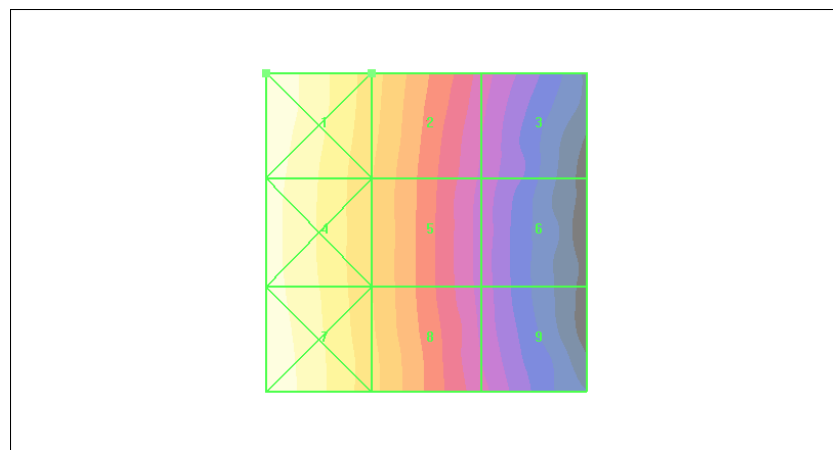
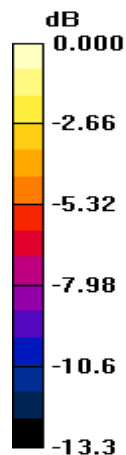
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.063 A/m; Power Drift = 0.156 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.124 M4	Grid 2 0.086 M4	Grid 3 0.053 M4
Grid 4 0.118 M4	Grid 5 0.083 M4	Grid 6 0.049 M4
Grid 7 0.123 M4	Grid 8 0.085 M4	Grid 9 0.052 M4



0 dB = 0.124 A/m

Figure 54 HAC RF H-Field WCDMA Band V Channel 4233

TA Technology (Shanghai) Co., Ltd.

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HAC RF H-Field WCDMA Band V Middle

Date/Time: 1/16/2012 8:37:07 PM

Communication System: WCDMA Band V; Frequency: 836.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.070 A/m

Probe Modulation Factor = 1.01

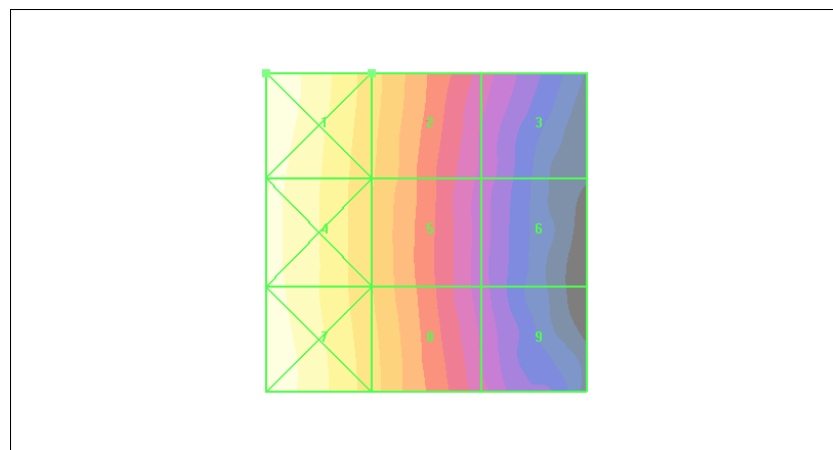
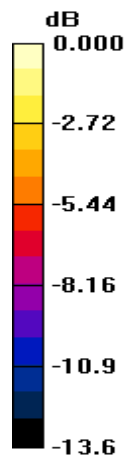
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.052 A/m; Power Drift = 0.026 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.102 M4	Grid 2 0.070 M4	Grid 3 0.043 M4
Grid 4 0.097 M4	Grid 5 0.068 M4	Grid 6 0.039 M4
Grid 7 0.101 M4	Grid 8 0.070 M4	Grid 9 0.042 M4



0 dB = 0.102 A/m

Figure 55 HAC RF H-Field WCDMA Band V Channel 4183

TA Technology (Shanghai) Co., Ltd.

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HAC RF H-Field WCDMA Band V Low

Date/Time: 1/16/2012 8:47:30 PM

Communication System: WCDMA Band V; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility

Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.073 A/m

Probe Modulation Factor = 1.01

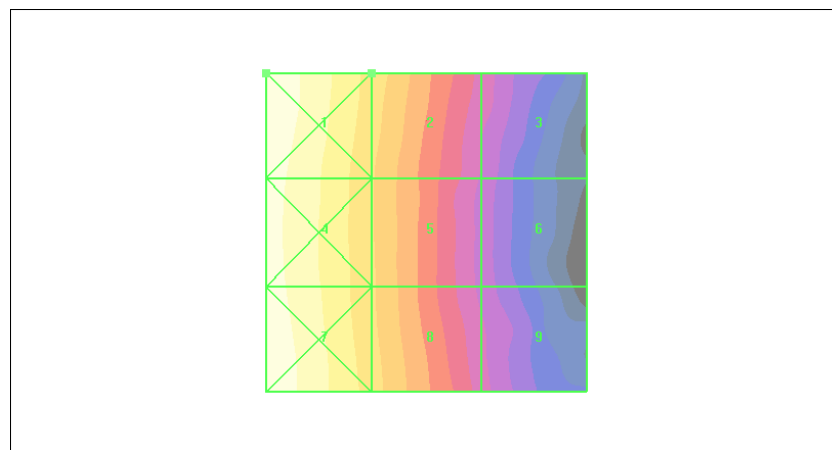
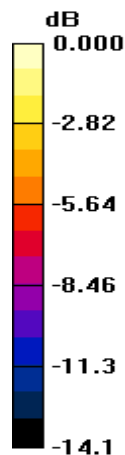
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.052 A/m; Power Drift = 0.158 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.105 M4	Grid 2 0.073 M4	Grid 3 0.043 M4
Grid 4 0.100 M4	Grid 5 0.069 M4	Grid 6 0.039 M4
Grid 7 0.104 M4	Grid 8 0.072 M4	Grid 9 0.042 M4



0 dB = 0.105A/m

Figure 56 HAC RF H-Field WCDMA Band V Channel 4132

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HAC RF H-Field WCDMA Band V HSDPA High

Date/Time: 1/16/2012 10:34:34 PM

Communication System: WCDMA Band V + HSDPA(8); Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device High/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.085 A/m

Probe Modulation Factor = 1.01

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.062 A/m; Power Drift = 0.016 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.122 M4	Grid 2 0.085 M4	Grid 3 0.052 M4
Grid 4 0.116 M4	Grid 5 0.082 M4	Grid 6 0.048 M4
Grid 7 0.121 M4	Grid 8 0.085 M4	Grid 9 0.052 M4

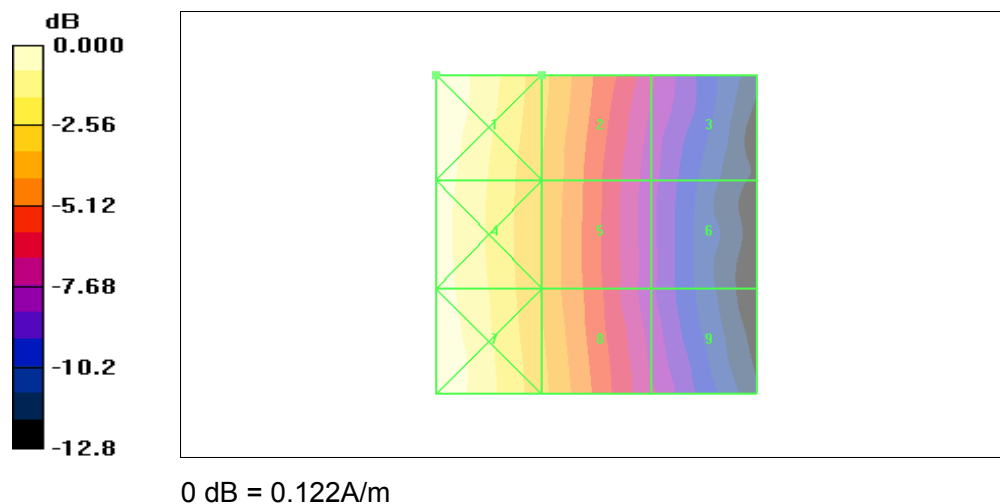


Figure 57 HAC RF H-Field WCDMA Band V HSDPA Channel 4233

TA Technology (Shanghai) Co., Ltd.

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HAC RF H-Field WCDMA Band V HSDPA Middle

Date/Time: 1/16/2012 10:29:44 PM

Communication System: WCDMA Band V + HSDPA(8); Frequency: 836.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Middle/Hearing Aid

Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.070 A/m

Probe Modulation Factor = 1.01

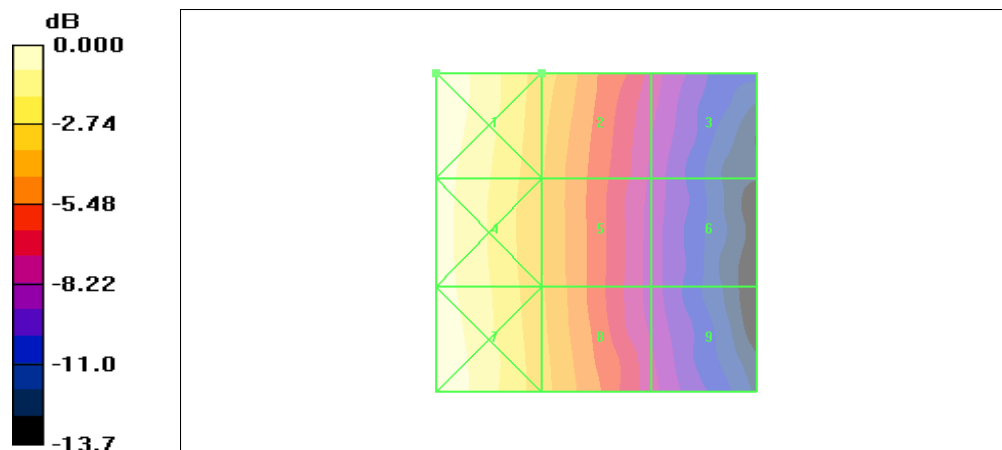
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.051 A/m; Power Drift = 0.038 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.101 M4	Grid 2 0.070 M4	Grid 3 0.042 M4
Grid 4 0.096 M4	Grid 5 0.067 M4	Grid 6 0.038 M4
Grid 7 0.100 M4	Grid 8 0.069 M4	Grid 9 0.041 M4



0 dB = 0.101A/m

Figure 58 HAC RF H-Field WCDMA Band V HSDPA Channel 4183

TA Technology (Shanghai) Co., Ltd.
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HAC RF H-Field WCDMA Band V HSDPA Low

Date/Time: 1/16/2012 10:39:24 PM

Communication System: WCDMA Band V + HSDPA(8); Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Ambient Temperature: 22.3 °C

Phantom section: RF Section

DASY4 Configuration:

Probe: H3DV6 - SN6187; Calibrated: 06/17/2011

Electronics: DAE4 Sn871; Calibrated: 11/22/2011

Phantom: HAC Test Arch; Type: SD HAC P01 BA;

Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the Device Low/Hearing Aid Compatibility Test (101x101x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.072 A/m

Probe Modulation Factor = 1.01

Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.052 A/m; Power Drift = 0.064 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1 0.104 M4	Grid 2 0.071 M4	Grid 3 0.043 M4
Grid 4 0.099 M4	Grid 5 0.069 M4	Grid 6 0.039 M4
Grid 7 0.104 M4	Grid 8 0.072 M4	Grid 9 0.044 M4

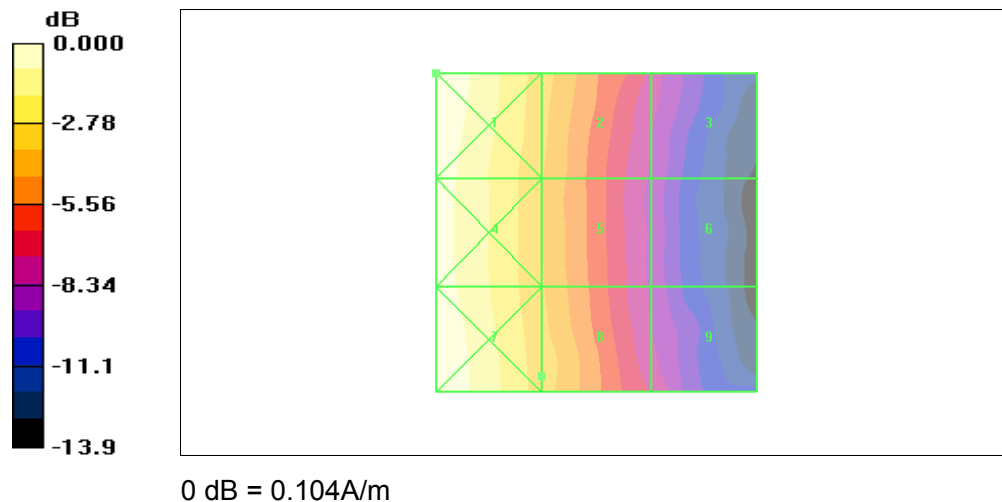


Figure 59 HAC RF H-Field WCDMA Band V HSDPA Channel 4132

TA Technology (Shanghai) Co., Ltd.

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ANNEX C: E-Probe Calibration Certificate

Calibration Laboratory of
Schmid & Partner
Engineering AG
Zeughausstrasse 43, 8004 Zurich, Switzerland



S Schweizerischer Kalibrierdienst
S Service suisse d'étalonnage
S Servizio svizzero di taratura
S Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)
The Swiss Accreditation Service is one of the signatories to the EA
Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: SCS 108

Client

Auden

Certificate No: ER3-2302_Jun11

CALIBRATION CERTIFICATE

Object: ER3DV6 - SN:2302

Calibration procedure(s): QA CAL-02.v6, QA CAL-25.v4
Calibration procedure for E-field probes optimized for close near field
evaluations in air.

Calibration date: June 15, 2011

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).
The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.

All calibrations have been conducted in the closed laboratory facility: environment temperature $(22 \pm 3)^{\circ}\text{C}$ and humidity $< 70\%$.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID	Cal Date (Certificate No.)	Scheduled Calibration
Power meter E4419B	GB41293874	31-Mar-11 (No. 217-01372)	Apr-12
Power sensor E4412A	MY41498087	31-Mar-11 (No. 217-01372)	Apr-12
Reference 3 dB Attenuator	SN: S5054 (3c)	29-Mar-11 (No. 217-01369)	Apr-12
Reference 20 dB Attenuator	SN: S5086 (20b)	29-Mar-11 (No. 217-01367)	Apr-12
Reference 30 dB Attenuator	SN: S5129 (30b)	29-Mar-11 (No. 217-01370)	Apr-12
Reference Probe ER3DV6	SN: 2328	4-Oct-10 (No. ER3-2328_Oct10)	Oct-11
DAE4	SN: 789	6-Apr-11 (No. DAE4-789_Apr11)	Apr-12
Secondary Standards	ID	Check Date (in house)	Scheduled Check
RF generator HP 8648C	US3642UD1700	4-Aug-09 (in house check Oct-09)	In house check: Oct-11
Network Analyzer HP 8753E	US37380585	18-Oct-01 (in house check Oct-10)	In house check: Oct-11

	Name	Function	Signature
Calibrated by:	Jeton Kasrat	Laboratory Technician	
Approved by:	Katja Pokovic	Technical Manager	
This calibration certificate shall not be reproduced except in full without written approval of the laboratory.			
Issued: June 17, 2011			

TA Technology (Shanghai) Co., Ltd.

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Calibration Laboratory of
Schmid & Partner
Engineering AG
Zeughausstrasse 43, 8004 Zurich, Switzerland



S Schweizerischer Kalibrierdienst
C Service suisse d'étalonnage
S Servizio svizzero di taratura
Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)
The Swiss Accreditation Service is one of the signatories to the EA
Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: **SCS 108**

Glossary:

NORM _{x,y,z}	sensitivity in free space
DCP	diode compression point
CF	crest factor (1/duty_cycle) of the RF signal
A, B, C	modulation dependent linearization parameters
Polarization ϕ	ϕ rotation around probe axis
Polarization θ	θ rotation around an axis that is in the plane normal to probe axis (at measurement center), i.e., $\theta = 0$ is normal to probe axis
Connector Angle	information used in DASY system to align probe sensor X to the robot coordinate system

Calibration is Performed According to the Following Standards:

- a) IEEE Std 1309-2005, "IEEE Standard for calibration of electromagnetic field sensors and probes, excluding antennas, from 9 kHz to 40 GHz", December 2005.

Methods Applied and Interpretation of Parameters:

- NORM_{x,y,z}**: Assessed for E-field polarization $\theta = 0$ for XY sensors and $\theta = 90$ for Z sensor ($f \leq 900$ MHz in TEM-cell; $f > 1800$ MHz: R22 waveguide).
- NORM(f)_{x,y,z}** = NORM_{x,y,z} * frequency_response (see Frequency Response Chart).
- DCP_{x,y,z}**: DCP are numerical linearization parameters assessed based on the data of power sweep with CW signal (no uncertainty required). DCP does not depend on frequency nor media.
- PAR**: PAR is the Peak to Average Ratio that is not calibrated but determined based on the signal characteristics
- A_{x,y,z}; B_{x,y,z}; C_{x,y,z}; VR_{x,y,z}**: A, B, C are numerical linearization parameters assessed based on the data of power sweep for specific modulation signal. The parameters do not depend on frequency nor media. VR is the maximum calibration range expressed in RMS voltage across the diode.
- Spherical isotropy (3D deviation from isotropy)**: in a locally homogeneous field realized using an open waveguide setup.
- Sensor Offset**: The sensor offset corresponds to the offset of virtual measurement center from the probe tip (on probe axis). No tolerance required.
- Connector Angle**: The angle is assessed using the information gained by determining the NORM_x (no uncertainty required).

ER3DV6 – SN:2302

June 15, 2011

Probe ER3DV6

SN:2302

Manufactured: November 6, 2002
Calibrated: June 15, 2011

Calibrated for DASY/EASY Systems
(Note: non-compatible with DASY2 system!)

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ER3DV6- SN:2302

June 15, 2011

DASY/EASY - Parameters of Probe: ER3DV6 - SN:2302

Basic Calibration Parameters

	Sensor X	Sensor Y	Sensor Z	Unc (k=2)
Norm ($\mu\text{V}/(\text{V/m})^2$)	1.47	1.34	1.44	$\pm 10.1 \%$
DCP (mV) ^a	98.2	96.7	101.8	

Modulation Calibration Parameters

UID	Communication System Name	PAR		A dB	B dB	C dB	VR mV	Unc ^E (k=2)
10000	CW	0.00	X	0.00	0.00	1.00	113.8	$\pm 3.0 \%$
			Y	0.00	0.00	1.00	99.1	
			Z	0.00	0.00	1.00	95.3	

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor $k=2$, which for a normal distribution corresponds to a coverage probability of approximately 95%.

^a Numerical linearization parameter: uncertainty not required.

^E Uncertainty is determined using the max. deviation from linear response applying rectangular distribution and is expressed for the square of the field value.

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Test Report

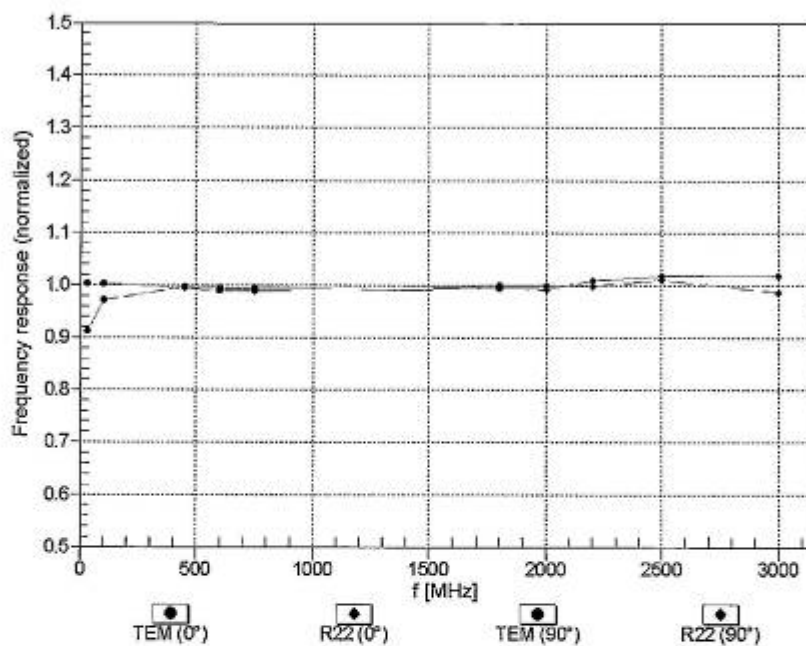
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ER3DV6-SN:2302

June 15, 2011

Frequency Response of E-Field
(TEM-Cell:ifi110 EXX, Waveguide: R22)



Uncertainty of Frequency Response of E-field: $\pm 6.3\%$ ($k=2$)

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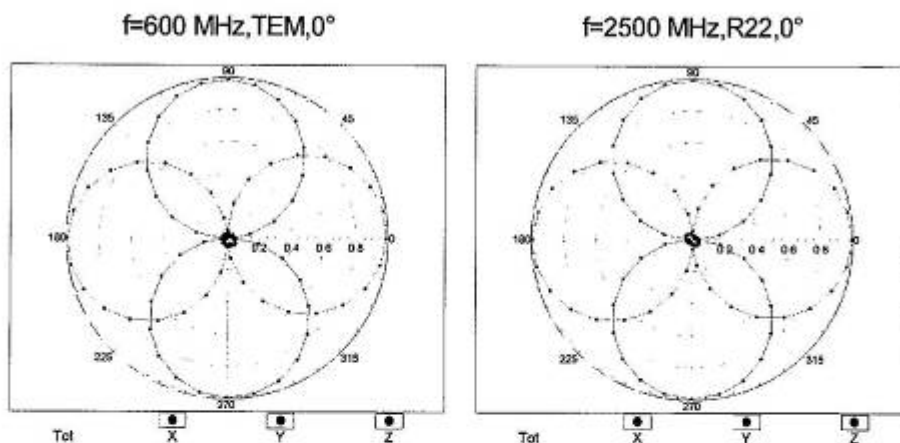
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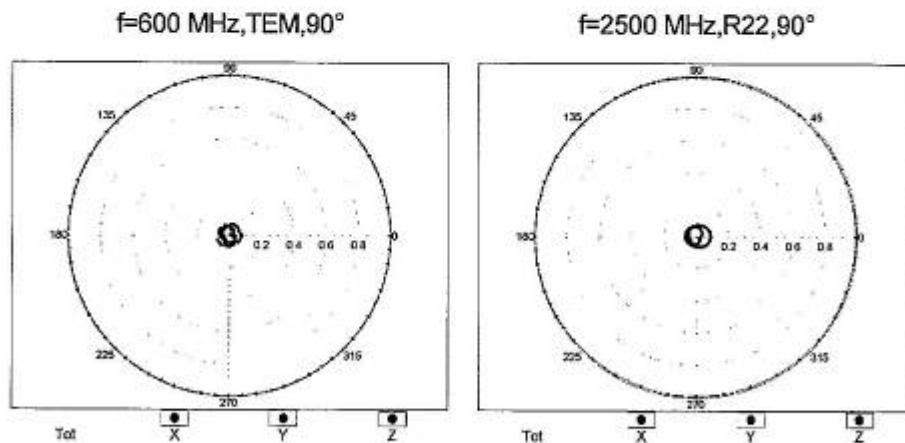
ER3DV6- SN:2302

June 15, 2011

Receiving Pattern (ϕ), $\vartheta = 0^\circ$



Receiving Pattern (ϕ), $\vartheta = 90^\circ$



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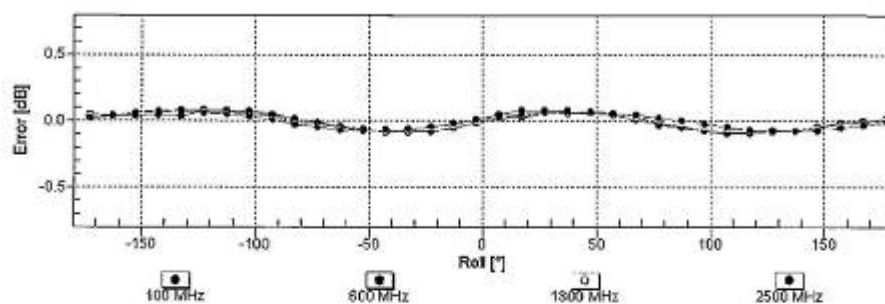
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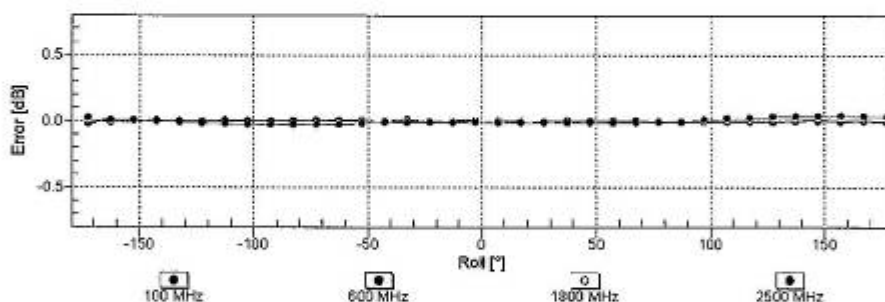
June 15, 2011

Receiving Pattern (ϕ), $\vartheta = 0^\circ$



Uncertainty of Axial Isotropy Assessment: $\pm 0.5\%$ ($k=2$)

Receiving Pattern (ϕ), $\vartheta = 90^\circ$



Uncertainty of Axial Isotropy Assessment: $\pm 0.5\%$ ($k=2$)

TA Technology (Shanghai) Co., Ltd.
Test Report

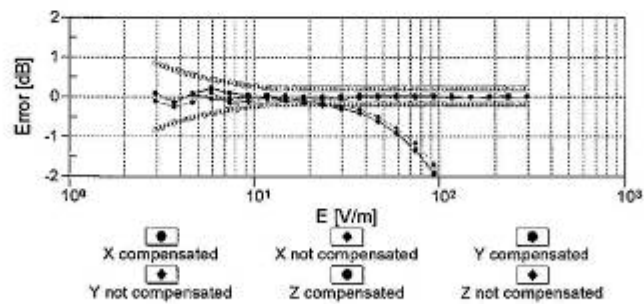
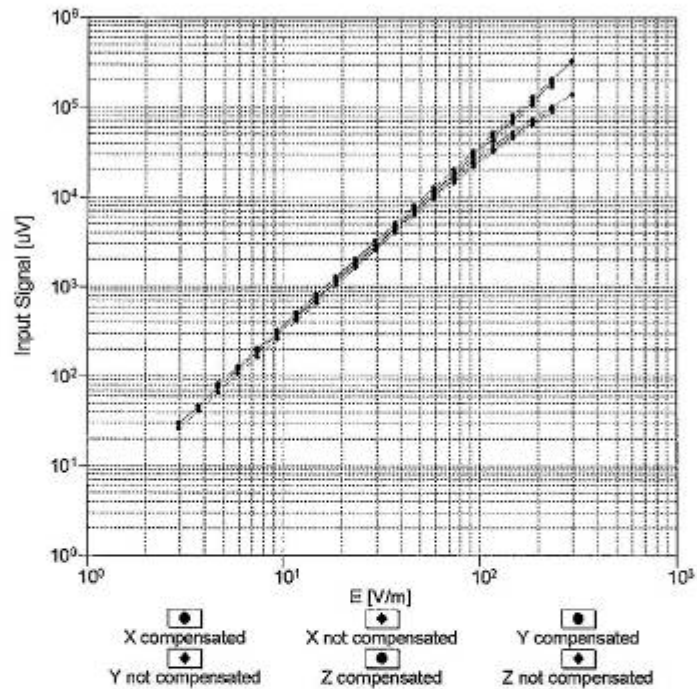
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ER3DV6-SN:2302

June 15, 2011

Dynamic Range f(E-field)
(TEM cell , f = 900 MHz)



Uncertainty of Linearity Assessment: $\pm 0.6\%$ (k=2)

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Test Report

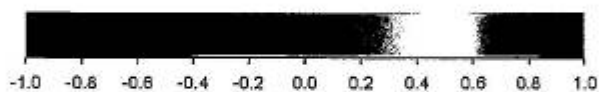
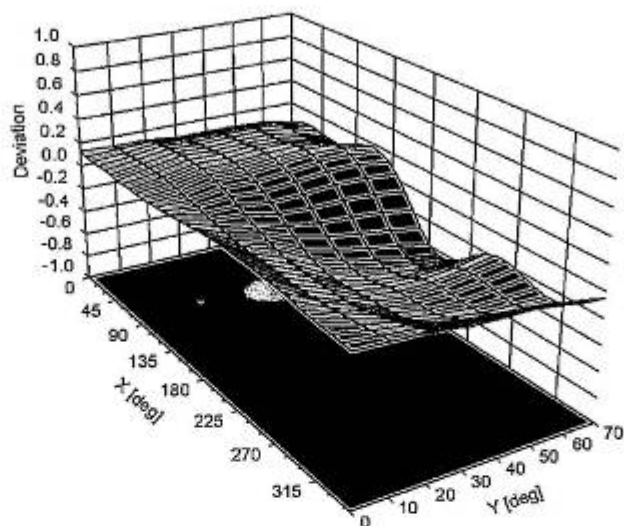
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ER3DV6-SN:2302

June 15, 2011

Deviation from Isotropy in Air
Error (ϕ , θ), $f = 900$ MHz



Uncertainty of Spherical Isotropy Assessment: $\pm 2.6\%$ ($k=2$)

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ER3DV6- SN:2302

June 15, 2011

DASY/EASY - Parameters of Probe: ER3DV6 - SN:2302

Other Probe Parameters

Sensor Arrangement	Rectangular
Connector Angle (°)	-2.7
Mechanical Surface Detection Mode	enabled
Optical Surface Detection Mode	disabled
Probe Overall Length	337 mm
Probe Body Diameter	10 mm
Tip Length	10 mm
Tip Diameter	8 mm
Probe Tip to Sensor X Calibration Point	2.5 mm
Probe Tip to Sensor Y Calibration Point	2.5 mm
Probe Tip to Sensor Z Calibration Point	2.5 mm

TA Technology (Shanghai) Co., Ltd.

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ANNEX D: H-Probe Calibration Certificate

Calibration Laboratory of
Schmid & Partner
Engineering AG
Zeughausstrasse 43, 8004 Zurich, Switzerland



S Schweizerischer Kalibrierdienst
C Service suisse d'étalonnage
S Servizio svizzero di taratura
S Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)
The Swiss Accreditation Service is one of the signatories to the EA
Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: **SCS 108**

Client

Auden

Certificate No: **H3-6187_Jun11**

CALIBRATION CERTIFICATE

Object: **H3DV6 - SN:6187**

Calibration procedure(s): **QA-CAL-03.v6; QA-CAL-25.v4**
Calibration procedure for H-field probes optimized for close near field evaluations in air

Calibration date: **June 17, 2011**

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).
The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.

All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3 °C) and humidity < 70%.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID	Cal Date (Certificate No.)	Scheduled Calibration
Power meter E4419B	GB41293674	31-Mar-11 (No. 217-01372)	Apr-12
Power sensor E4412A	MY41488087	31-Mar-11 (No. 217-01372)	Apr-12
Reference 3 dB Attenuator	SN: S5054 (3c)	29-Mar-11 (No. 217-01369)	Apr-12
Reference 20 dB Attenuator	SN: S5086 (20b)	29-Mar-11 (No. 217-01367)	Apr-12
Reference 30 dB Attenuator	SN: S5129 (30b)	29-Mar-11 (No. 217-01370)	Apr-12
Reference Probe H3DV6	SN: 6182	4-Oct-10 (No. H3-6182_Oct10)	Oct-11
DAE4	SN: 789	6-Apr-11 (No. DAE4-789_Apr11)	Apr-12
Secondary Standards	ID	Check Date (in house)	Scheduled Check
RF generator HP 8648C	US3642U01700	4-Aug-99 (in house check Oct-09)	In house check: Oct-11
Network Analyzer HP 8753E	US37390585	18-Oct-01 (in house check Oct-10)	In house check: Oct-11

Calibrated by:	Name Claudio Leubler	Function Laboratory Technician	Signature
Approved by:	Name Karla Pokovic	Function Technical Manager	Signature

Issued: June 17, 2011

This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

TA Technology (Shanghai) Co., Ltd.

Test Report

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**Calibration Laboratory of
Schmid & Partner
Engineering AG**
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Accreditation No.: **SCS 108**

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Glossary:

NORM _{x,y,z}	sensitivity in free space
DCP	diode compression point
CF	crest factor (1/duty_cycle) of the RF signal
A, B, C	modulation dependent linearization parameters
Polarization ϕ	ϕ rotation around probe axis
Polarization θ	θ rotation around an axis that is in the plane normal to probe axis (at measurement center), i.e., $\theta = 0$ is normal to probe axis
Connector Angle	information used in DASY system to align probe sensor X to the robot coordinate system

Calibration is Performed According to the Following Standards:

- a) IEEE Std 1309-2005, "IEEE Standard for calibration of electromagnetic field sensors and probes, excluding antennas, from 9 kHz to 40 GHz", December 2005.

Methods Applied and Interpretation of Parameters:

- NORM_{x,y,z}**: Assessed for E-field polarization $\theta = 0$ for XY sensors and $\theta = 90$ for Z sensor ($f \leq 900$ MHz in TEM-cell; $f > 1800$ MHz: R22 waveguide).
- X, Y, Z(f)**: $X_{a0a1a2} = X, Y, Z_{a0a1a2} \cdot \text{frequency_response}$ (see Frequency Response Chart).
- DCP_{x,y,z}**: DCP are numerical linearization parameters assessed based on the data of power sweep with CW signal (no uncertainty required). DCP does not depend on frequency nor media.
- PAR**: PAR is the Peak to Average Ratio that is not calibrated but determined based on the signal characteristics
- A_{x,y,z}; B_{x,y,z}; C_{x,y,z}; VR_{x,y,z}**: A, B, C are numerical linearization parameters assessed based on the data of power sweep for specific modulation signal. The parameters do not depend on frequency nor media. VR is the maximum calibration range expressed in RMS voltage across the diode.
- Spherical isotropy (3D deviation from isotropy)**: in a locally homogeneous field realized using an open waveguide setup.
- Sensor Offset**: The sensor offset corresponds to the offset of virtual measurement center from the probe tip (on probe axis). No tolerance required.
- Connector Angle**: The angle is assessed using the information gained by determining the X_{a0a1a2} (no uncertainty required).

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H3DV6 – SN:6187

June 17, 2011

Probe H3DV6

SN:6187

Manufactured: June 8, 2004
Calibrated: June 17, 2011

Calibrated for DASY/EASY Systems
(Note: non-compatible with DASY2 system!)

TA Technology (Shanghai) Co., Ltd.

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H3DV6- SN:6187

June 17, 2011

DASY/EASY - Parameters of Probe: H3DV6 - SN:6187

Basic Calibration Parameters

		Sensor X	Sensor Y	Sensor Z	Unc (k=2)
Norm (A/m / $\sqrt{\text{mV}}$)	a0	3.25E-003	2.53E-003	3.06E-003	$\pm 5.1 \%$
Norm (A/m / $\sqrt{\text{mV}}$)	a1	-2.03E-005	4.43E-005	-4.88E-005	$\pm 5.1 \%$
Norm (A/m / $\sqrt{\text{mV}}$)	a2	2.36E-005	1.59E-005	7.21E-005	$\pm 5.1 \%$
DCP (mV) ^B		108.1	92.6	91.8	

Modulation Calibration Parameters

UID	Communication System Name	PAR		A dB	B dB	C dB	VR mV	Unc ^E (k=2)
10000	CW	0.00	X	0.00	0.00	1.00	77.7	$\pm 3.0 \%$
			Y	0.00	0.00	1.00	72.9	
			Z	0.00	0.00	1.00	90.7	

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor $k=2$, which for a normal distribution corresponds to a coverage probability of approximately 95%.

^B Numerical linearization parameter; uncertainty not required.

^E Uncertainty is determined using the max. deviation from linear response applying rectangular distribution and is expressed for the square of the field value.

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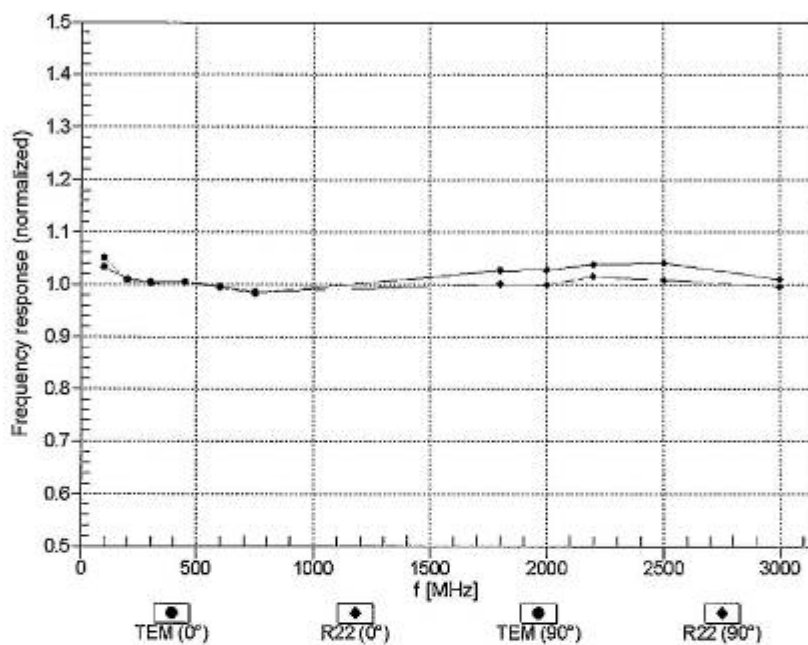
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H3DV6- SN:6187

June 17, 2011

Frequency Response of H-Field
(TEM-Cell:ifi110 EXX, Waveguide: R22)



Uncertainty of Frequency Response of H-field: $\pm 6.3\%$ (k=2)

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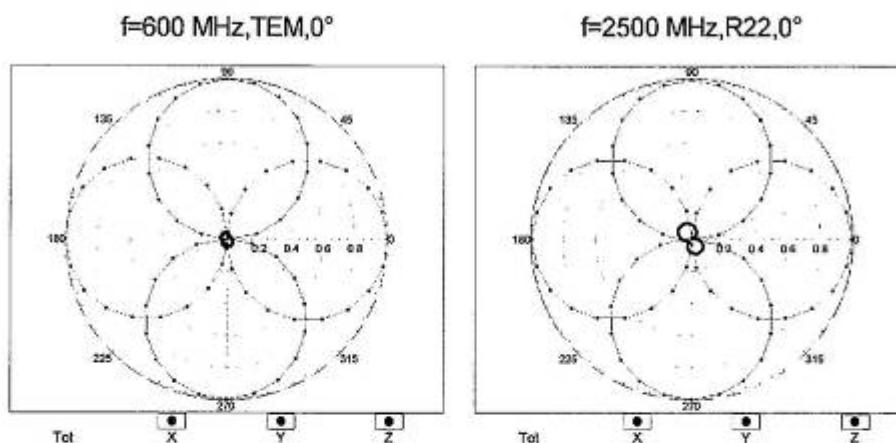
Report No. RZA1201-0064HAC01R2

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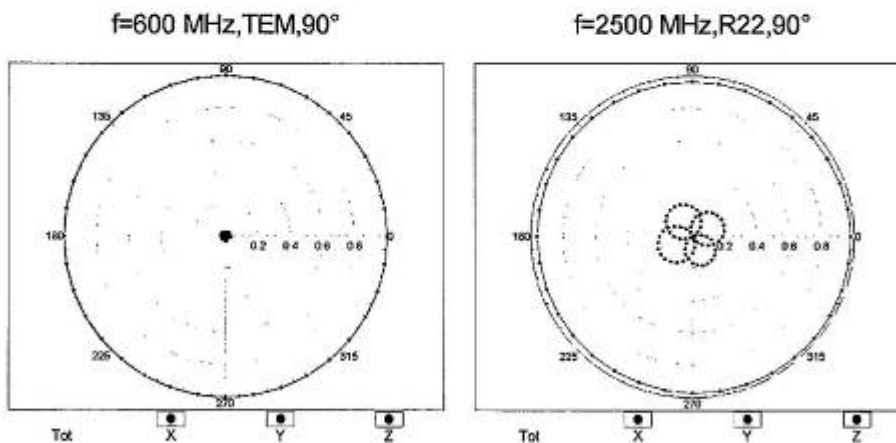
H3DV6- SN:8187

June 17, 2011

Receiving Pattern (ϕ), $\theta = 0^\circ$



Receiving Pattern (ϕ), $\theta = 90^\circ$



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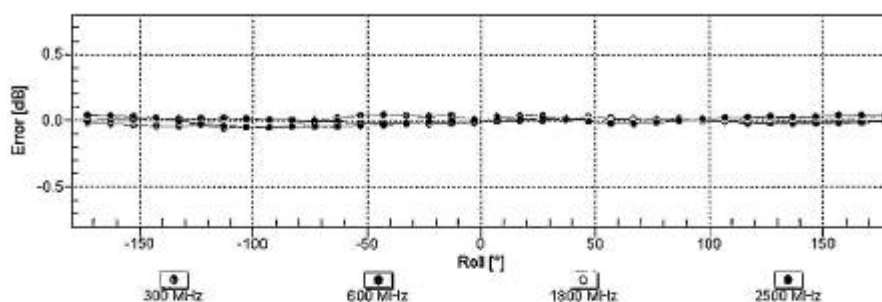
Report No. RZA1201-0064HAC01R2

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H3DV6- SN:6187

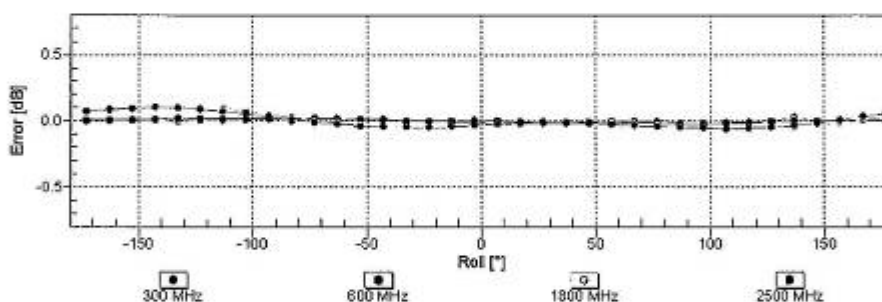
June 17, 2011

Receiving Pattern (ϕ), $\vartheta = 0^\circ$



Uncertainty of Axial Isotropy Assessment: $\pm 0.5\%$ ($k=2$)

Receiving Pattern (ϕ), $\vartheta = 90^\circ$



Uncertainty of Axial Isotropy Assessment: $\pm 0.5\%$ ($k=2$)

TA Technology (Shanghai) Co., Ltd. Test Report

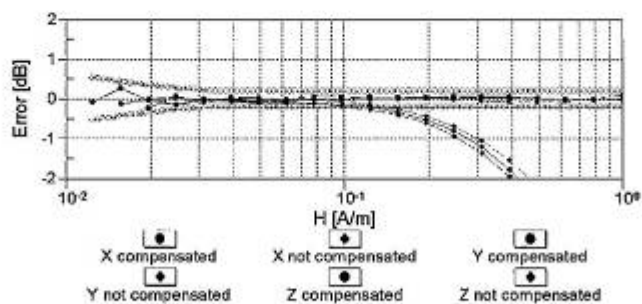
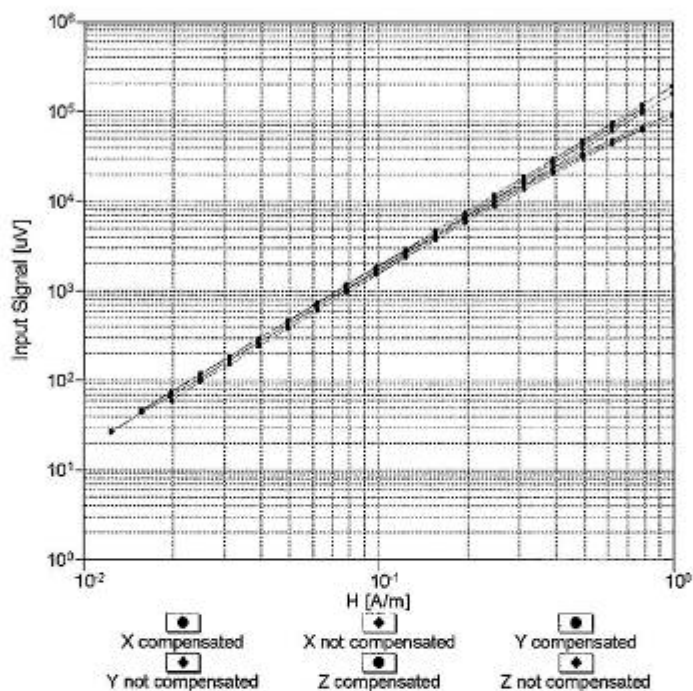
Report No. RZA1201-0064HAC01R2

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H3DV6- SN:6167

June 17, 2011

Dynamic Range f(H-field) (TEM cell, f = 900 MHz)



Uncertainty of Linearity Assessment: $\pm 0.6\%$ (k=2)

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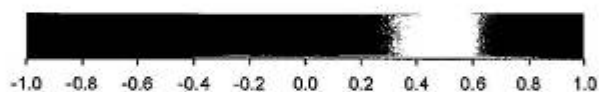
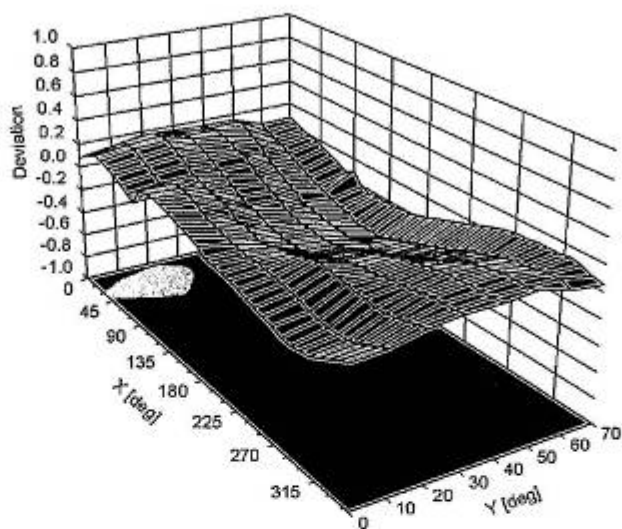
Report No. RZA1201-0064HAC01R2

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H3DV6- SN:6167

June 17, 2011

Deviation from Isotropy in Air
Error (ϕ , θ), $f = 900$ MHz



Uncertainty of Spherical Isotropy Assessment: $\pm 2.6\%$ ($k=2$)

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H3DV6- SN:6187

June 17, 2011

DASY/EASY - Parameters of Probe: H3DV6 - SN:6187

Other Probe Parameters

Sensor Arrangement	Rectangular
Connector Angle (°)	-113
Mechanical Surface Detection Mode	enabled
Optical Surface Detection Mode	disabled
Probe Overall Length	337 mm
Probe Body Diameter	10 mm
Tip Length	20 mm
Tip Diameter	6 mm
Probe Tip to Sensor X Calibration Point	3 mm
Probe Tip to Sensor Y Calibration Point	3 mm
Probe Tip to Sensor Z Calibration Point	3 mm

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ANNEX E: CD835V3 Dipole Calibration Certificate

Calibration Laboratory of
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Zeughausstrasse 43, 8004 Zurich, Switzerland



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Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: **SCS 108**

Client **TA Technology (Auden)**

Certificate No: **CD835V3-1133_Apr09**

CALIBRATION CERTIFICATE

Object **CD835V3 - SN: 1133**

Calibration procedure(s) **QA CAL-20.v4**
Calibration procedure for dipoles in air

Calibration date: **April 22, 2009**

Condition of the calibrated item **In Tolerance**

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).
All calibrations have been conducted in the closed laboratory facility; environment temperature $(22 \pm 3)^{\circ}\text{C}$ and humidity $< 70\%$.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID #	Cal Date (Certificate No.)	Scheduled Calibration
Power meter EPM-442A	GB37480704	08-Oct-08 (No. 217-00898)	Oct-09
Power sensor HP 8481A	US37292783	08-Oct-08 (No. 217-00898)	Oct-09
Probe ER3DV6	SN: 2336	22-Dec-08 (No. ER3-2336_Dec08)	Dec-09
Probe H3DV6	SN: 6065	22-Dec-08 (No. H3-6065_Dec08)	Dec-09
DAE4	SN: 781	20-Feb-09 (No. DAE4-781_Feb09)	Feb-10
Secondary Standards	ID #	Check Date (in house)	Scheduled Check
Power meter R&S NRP	SN: 101748	23-Sep-08 (in house check Dec-08)	In house check: Dec-10
Power sensor R&S NRP-Z91	SN: 100711	25-Aug-08 (in house check Dec-08)	In house check: Dec-10
Power sensor R&S NRP-Z91	SN: 100712	25-Aug-08 (in house check Dec-08)	In house check: Dec-10
Network Analyzer HP 8753E	US37390585	18-Oct-01 (in house check Oct-08)	In house check: Oct-09
RF generator E4433B	MY 41310391	03-Nov-04 (in house check Oct-07)	In house check: Oct-09

	Name	Function	Signature
Calibrated by:	Mike Melli	Laboratory Technician	
Approved by:	Fin Bornholt	Technical Director	

Issued: April 24, 2009

This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

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Accreditation No.: **SCS 108**

References

- [1] ANSI-C63.19-2006
American National Standard for Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.
- [2] ANSI-C63.19-2007
American National Standard for Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- **Coordinate System:** y-axis is in the direction of the dipole arms, z-axis is from the basis of the antenna (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes. In coincidence with the standards [1, 2], the measurement planes (probe sensor center) are selected to be at a distance of 10 mm above the top edge of the dipole arms.
- **Measurement Conditions:** Further details are available from the hardcopies at the end of the certificate. All figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- **Antenna Positioning:** The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY4 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- **Feed Point Impedance and Return Loss:** These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- **E-field distribution:** E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1, 2], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 10 mm (in z) above the top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, 10mm above the dipole surface.
- **H-field distribution:** H-field is measured with an isotropic H-field probe with 100mW forward power to the antenna feed point, in the x-y-plane. The scan area and sensor distance is equivalent to the E-field scan. The maximum of the field is available at the center (subgrid 5) above the feed point. The H-field value stated as calibration value represents the maximum of the interpolated H-field, 10mm above the dipole surface at the feed point.

TA Technology (Shanghai) Co., Ltd.

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1 Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY4	V4.7 B80
DASY PP Version	SEMCAD	V1.8 B186
Phantom	HAC Test Arch	SD HAC P01 BA, #1070
Distance Dipole Top - Probe Center	10 mm	
Scan resolution	dx, dy = 5 mm	area = 20 x 180 mm
Frequency	835 MHz $\pm$ 1 MHz	
Forward power at dipole connector	20.0 dBm = 100mW	
Input power drift	< 0.05 dB	

2 Maximum Field values

H-field 10 mm above dipole surface	condition	interpolated maximum
Maximum measured	100 mW forward power	0.446 A/m

Uncertainty for H-field measurement: 8.2% (k=2)

E-field 10 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end-	100 mW forward power	158.2 V/m
Maximum measured above low end	100 mW forward power	157.3 V/m
Averaged maximum above arm	100 mW forward power	157.8 V/m

Uncertainty for E-field measurement: 12.8% (k=2)

3 Appendix

3.1 Antenna Parameters

Frequency	Return Loss	Impedance
800 MHz	18.2 dB	(43.3 – j12.9) Ohm
835 MHz	33.2 dB	(49.3 + j2.1) Ohm
900 MHz	17.4 dB	(53.5 – j13.6) Ohm
950 MHz	20.0 dB	(44.3 + j7.5) Ohm
960 MHz	14.8 dB	(53.2 + j18.8) Ohm

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

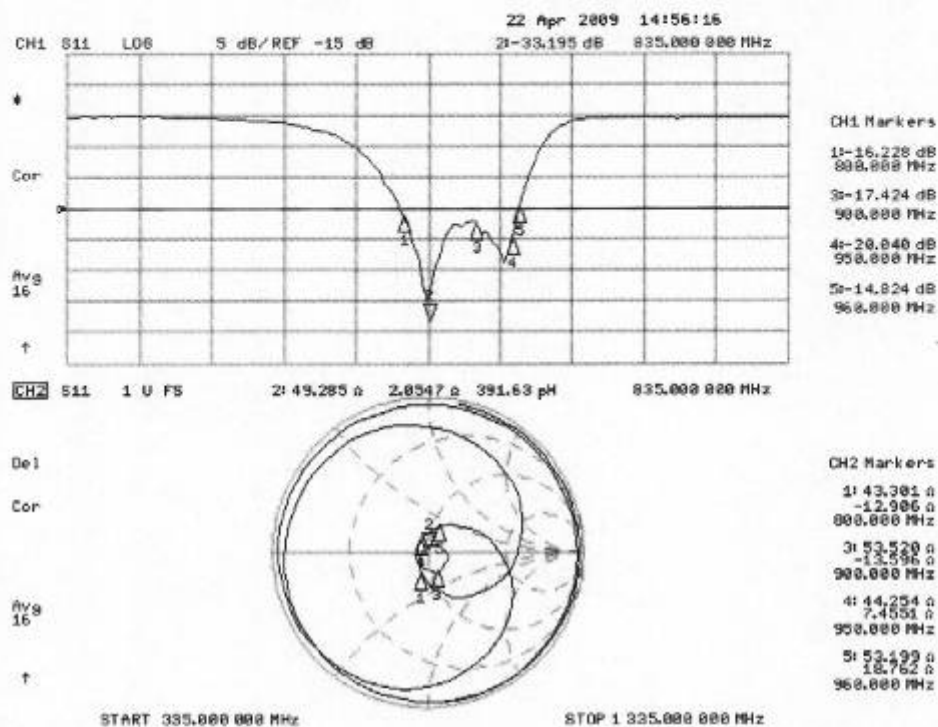
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3.3 Measurement Sheets

3.3.1 Return Loss and Smith Chart



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3.3.2 DASY4 H-field Result

Date/Time: 21.04.2009 13:38:21

Test Laboratory: SPEAG Lab 2

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1133

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0 \text{ mho/m}$, $\epsilon_r = 1$; $\rho = 1 \text{ kg/m}^3$

Phantom section: RF Section

Measurement Standard: DASY4 (High Precision Assessment)

DASY4 Configuration:

- Probe: H3DV6 - SN6065; ; Calibrated: 22.12.2008
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 20.02.2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.446 A/m

Probe Modulation Factor = 1.00

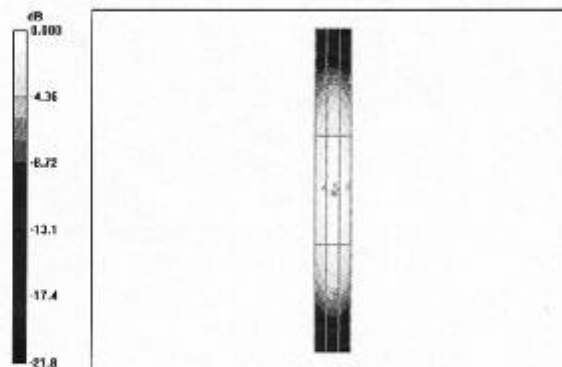
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.472 A/m; Power Drift = -0.006 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.364 M4	0.385 M4	0.368 M4
Grid 4	Grid 5	Grid 6
0.417 M4	0.446 M4	0.426 M4
Grid 7	Grid 8	Grid 9
0.365 M4	0.393 M4	0.376 M4



0 dB - 0.446 A/m

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3.3.3 DASY4 E-field Result

Date/Time: 22.04.2009 12:51:53

Test Laboratory: SPEAG Lab 2

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: 1133

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY4 (High Precision Assessment)

DASY4 Configuration:

- Probe: ER3DV6 - SN2336; ConvF(1, 1, 1); Calibrated: 22.12.2008
- Sensor-Surface: (Fix Surface)
- Electronics: DA64 Sn781; Calibrated: 20.02.2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 158.2 V/m

Probe Modulation Factor = 1.00

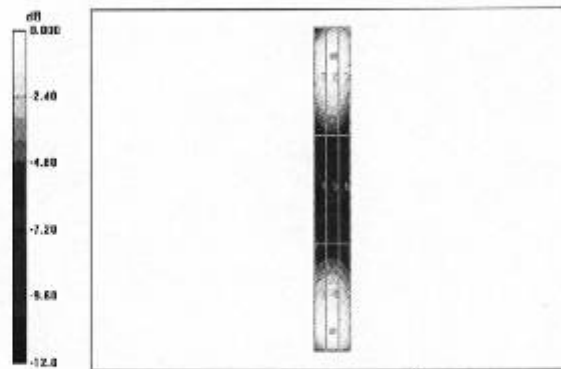
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 105.8 V/m; Power Drift = -0.013 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
152.4 M4	158.2 M4	154.6 M4
Grid 4	Grid 5	Grid 6
84.6 M4	86.9 M4	84.2 M4
Grid 7	Grid 8	Grid 9
151.7 M4	157.3 M4	152.4 M4



0 dB = 158.2 V/m

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ANNEX F: CD1880V3 Dipole Calibration Certificate

Calibration Laboratory of
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Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: SCS 108

Client **TA Technology (Auden)**

Certificate No: **CD1880V3-1115_Apr09**

CALIBRATION CERTIFICATE

Object **CD1880V3 - SN: 1115**

Calibration procedure(s) **QA CAL-20.v4
Calibration procedure for dipoles in air**

Calibration date: **April 22, 2009**

Condition of the calibrated item **In Tolerance**

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).
All calibrations have been conducted in the closed laboratory facility: environment temperature $(22 \pm 3)^{\circ}\text{C}$ and humidity $< 70\%$.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID #	Cal Date (Certificate No.)	Scheduled Calibration
Power meter EPM-442A	GB37480704	08-Oct-08 (No. 217-00898)	Oct-09
Power sensor HP 8481A	US37292783	08-Oct-08 (No. 217-00898)	Oct-09
Probe ER3DV6	SN: 2336	22-Dec-08 (No. ER3-2336_Dec08)	Dec-09
Probe H3DV6	SN: 6065	22-Dec-08 (No. H3-6065_Dec08)	Dec-09
DAE4	SN 781	20-Feb-09 (No. DAE4-781_Feb09)	Feb-10

Secondary Standards	ID #	Check Date (in house)	Scheduled Check
Power meter R&S NRP	SN: 101748	23-Sep-08 (in house check Dec-08)	In house check: Dec-10
Power sensor R&S NRP-Z91	SN: 100711	25-Aug-08 (in house check Dec-08)	In house check: Dec-10
Power sensor R&S NRP-Z91	SN: 100712	25-Aug-08 (in house check Dec-08)	In house check: Dec-10
Network Analyzer HP 8753E	US37390585	18-Oct-01 (in house check Oct-08)	In house check: Oct-09
RF generator E4433B	MY 41310391	22-Nov-04 (in house check Oct-07)	In house check: Oct-09

Calibrated by: **Name: Mike Mehl, Function: Laboratory Technician, Signature: [Signature]**

Approved by: **Name: Fin Bornholt, Function: Technical Director, Signature: [Signature]**

Issued: April 24, 2009

This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

Certificate No: CD1880V3-1115_Apr09

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Accreditation No.: **SCS 108**

References

- [1] ANSI-C63.19-2006
American National Standard for Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.
- [2] ANSI-C63.19-2007
American National Standard for Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- **Coordinate System:** y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes. In coincidence with the standards [1, 2], the measurement planes (probe sensor center) are selected to be at a distance of 10 mm above the top edge of the dipole arms.
- **Measurement Conditions:** Further details are available from the hardcopies at the end of the certificate. All figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- **Antenna Positioning:** The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY4 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- **Feed Point Impedance and Return Loss:** These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- **E-field distribution:** E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1, 2], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 10 mm (in z) above the top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, 10mm above the dipole surface.
- **H-field distribution:** H-field is measured with an isotropic H-field probe with 100mW forward power to the antenna feed point, in the x-y-plane. The scan area and sensor distance is equivalent to the E-field scan. The maximum of the field is available at the center (subgrid 5) above the feed point. The H-field value stated as calibration value represents the maximum of the interpolated H-field, 10mm above the dipole surface at the feed point.

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1. Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY4	V4.7 B80
DASY PP Version	SEMCAD	V1.8 B186
Phantom	HAC Test Arch	SD HAC P01 BA, #1070
Distance Dipole Top - Probe Center	10 mm	
Scan resolution	dx, dy = 5 mm	area = 20 x 90 mm
Frequency	1880 MHz $\pm$ 1 MHz	
Forward power at dipole connector	20.0 dBm = 100mW	
Input power drift	< 0.05 dB	

2. Maximum Field values

H-field 10 mm above dipole surface	condition	Interpolated maximum
Maximum measured	100 mW forward power	0.468 A/m

Uncertainty for H-field measurement: 8.2% (k=2)

E-field 10 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW forward power	140.5 V/m
Maximum measured above low end	100 mW forward power	138.2 V/m
Averaged maximum above arm	100 mW forward power	139.4 V/m

Uncertainty for E-field measurement: 12.8% (k=2)

3. Appendix

3.1 Antenna Parameters

Frequency	Return Loss	Impedance
1710 MHz	24.0 dB	(52.4 + j6.0) Ohm
1880 MHz	21.4 dB	(46.8 + j7.6) Ohm
1900 MHz	22.4 dB	(48.1 + j7.2) Ohm
1950 MHz	30.1 dB	(50.1 + j3.1) Ohm
2000 MHz	18.4 dB	(40.5 + j5.4) Ohm

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

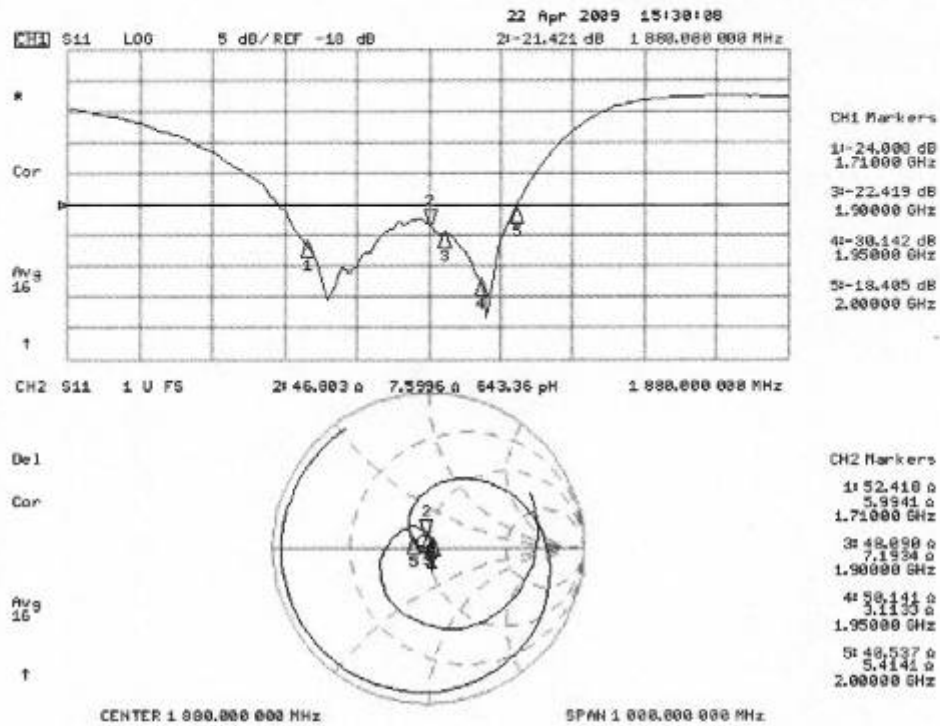
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3.3 Measurement Sheets

3.3.1 Return Loss and Smith Chart



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3.3.2 DASY4 H-Field Result

Date/Time: 21.04.2009 16:14:56

Test Laboratory: SPEAG Lab 2

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1115

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY4 (High Precision Assessment)

DASY4 Configuration:

- Probe: H3DV6 - SN6065; Calibrated: 22.12.2008
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 20.02.2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

H Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.468 A/m

Probe Modulation Factor = 1.00

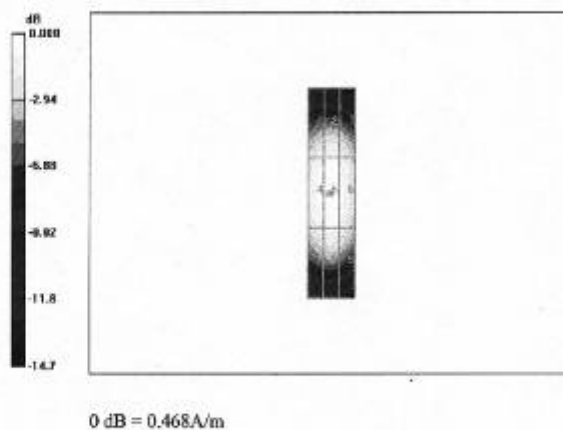
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 0.497 A/m; Power Drift = -0.028 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak H-field in A/m

Grid 1	Grid 2	Grid 3
0.410 M2	0.428 M2	0.405 M2
Grid 4	Grid 5	Grid 6
0.448 M2	0.468 M2	0.442 M2
Grid 7	Grid 8	Grid 9
0.409 M2	0.430 M2	0.403 M2



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3.3.3 DASY4 E-Field Result

Date/Time: 22.04.2009 15:33:14

Test Laboratory: SPEAG Lab 2

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: 1115

Communication System: CW; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY4 (High Precision Assessment)

DASY4 Configuration:

- Probe: ER3DV6 - SN2336; ConvF(1, 1); Calibrated: 22.12.2008
- Sensor Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 20.02.2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- Measurement SW: DASY4, V4.7 Build 80; Postprocessing SW: SEMCAD, V1.8 Build 186

E Scan - measurement distance from the probe sensor center to CD1880 Dipole = 10mm/Hearing Aid Compatibility Test (41x181x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 140.5 V/m

Probe Modulation Factor = 1.00

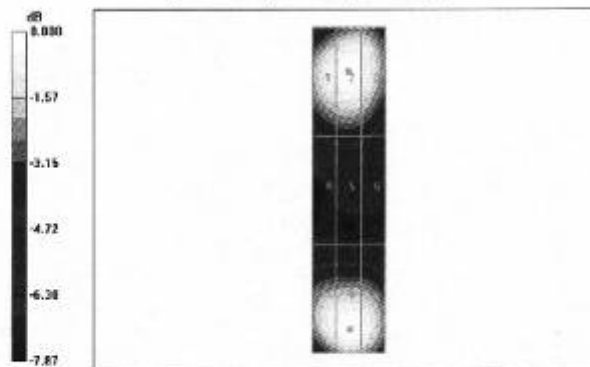
Device Reference Point: 0.000, 0.000, -6.30 mm

Reference Value = 157.9 V/m; Power Drift = 0.005 dB

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

Peak E-field in V/m

Grid 1	Grid 2	Grid 3
133.8 M2	138.2 M2	134.2 M2
Grid 4	Grid 5	Grid 6
90.3 M3	92.5 M3	88.2 M3
Grid 7	Grid 8	Grid 9
132.9 M2	140.5 M2	137.0 M2



0 dB = 140.5V/m

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ANNEX G: DAE4 Calibration Certificate

Calibration Laboratory of
Schmid & Partner
Engineering AG
Zeughausstrasse 43, 8004 Zurich, Switzerland



S Schweizerischer Kalibrierdienst
S Service suisse d'étalonnage
C Servizio svizzero di taratura
S Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)

Accreditation No.: **SCS 108**

The Swiss Accreditation Service is one of the signatories to the EA
Multilateral Agreement for the recognition of calibration certificates

Client **TA - SH (Auden)**

Certificate No: **DAE4-871_Nov11**

CALIBRATION CERTIFICATE

Object **DAE4 - SD 000 D04 BJ - SN: 871**

Calibration procedure(s) **QA CAL-06.v23**
Calibration procedure for the data acquisition electronics (DAE)

Calibration date: **November 22, 2011**

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).
The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.

All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID #	Cal Date (Certificate No.)	Scheduled Calibration
Keithley Multimeter Type 2001	SN: 0810278	28-Sep-11 (No:11450)	Sep-12
Secondary Standards	ID #	Check Date (in house)	Scheduled Check
Calibrator Box V1.1	SE UMS 006 AB 1004	08-Jun-11 (in house check)	In house check: Jun-12

Calibrated by:	Name	Function	Signature
	Andrea Gunti	Technician	
Approved by:	Name	Function	Signature
	Fin Bontholt	R&D Director	

Issued: November 22, 2011

This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

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Calibration Laboratory of
Schmid & Partner
Engineering AG
Zeughausstrasse 43, 8004 Zurich, Switzerland



S Schweizerischer Kalibrierdienst
C Service suisse d'étalonnage
S Servizio svizzero di taratura
S Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)
The Swiss Accreditation Service is one of the signatories to the EA
Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: **SCS 108**

Glossary

DAE data acquisition electronics
Connector angle information used in DASY system to align probe sensor X to the robot coordinate system.

Methods Applied and Interpretation of Parameters

- **DC Voltage Measurement:** Calibration Factor assessed for use in DASY system by comparison with a calibrated instrument traceable to national standards. The figure given corresponds to the full scale range of the voltmeter in the respective range.
- **Connector angle:** The angle of the connector is assessed measuring the angle mechanically by a tool inserted. Uncertainty is not required.
- The following parameters as documented in the Appendix contain technical information as a result from the performance test and require no uncertainty.
 - **DC Voltage Measurement Linearity:** Verification of the Linearity at +10% and -10% of the nominal calibration voltage. Influence of offset voltage is included in this measurement.
 - **Common mode sensitivity:** Influence of a positive or negative common mode voltage on the differential measurement.
 - **Channel separation:** Influence of a voltage on the neighbor channels not subject to an input voltage.
 - **AD Converter Values with inputs shorted:** Values on the internal AD converter corresponding to zero input voltage
 - **Input Offset Measurement:** Output voltage and statistical results over a large number of zero voltage measurements.
 - **Input Offset Current:** Typical value for information; Maximum channel input offset current, not considering the input resistance.
 - **Input resistance:** Typical value for information: DAE input resistance at the connector, during internal auto-zeroing and during measurement.
 - **Low Battery Alarm Voltage:** Typical value for information. Below this voltage, a battery alarm signal is generated.
 - **Power consumption:** Typical value for information. Supply currents in various operating modes.

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DC Voltage Measurement

A/D - Converter Resolution nominal

High Range: 1LSB = 6.1 μ V, full range = -100...+300 mV

Low Range: 1LSB = 61nV, full range = -1.....+3mV

DASY measurement parameters: Auto Zero Time: 3 sec; Measuring time: 3 sec

Calibration Factors	X	Y	Z
High Range	404.749 $\pm$ 0.1% (k=2)	404.733 $\pm$ 0.1% (k=2)	405.174 $\pm$ 0.1% (k=2)
Low Range	3.98175 $\pm$ 0.7% (k=2)	3.93601 $\pm$ 0.7% (k=2)	3.96830 $\pm$ 0.7% (k=2)

Connector Angle

Connector Angle to be used in DASY system	90.0 $^{\circ}$ $\pm$ 1 $^{\circ}$
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Appendix

1. DC Voltage Linearity

High Range	Reading (μV)	Difference (μV)	Error (%)
Channel X + Input	199991.9	-0.91	-0.00
Channel X + Input	20000.28	0.48	0.00
Channel X - Input	-19998.51	0.59	-0.00
Channel Y + Input	200003.0	1.24	0.00
Channel Y + Input	19999.67	0.17	0.00
Channel Y - Input	-20000.04	-0.34	0.00
Channel Z + Input	200010.1	-0.11	-0.00
Channel Z + Input	19999.33	-0.07	-0.00
Channel Z - Input	-20001.45	-0.85	0.00

Low Range	Reading (μV)	Difference (μV)	Error (%)
Channel X + Input	2000.0	0.05	0.00
Channel X + Input	199.81	-0.09	-0.04
Channel X - Input	-199.63	0.37	-0.19
Channel Y + Input	1999.9	-0.22	-0.01
Channel Y + Input	198.81	-1.19	-0.59
Channel Y - Input	-201.62	-1.72	0.86
Channel Z + Input	2000.4	0.48	0.02
Channel Z + Input	199.30	-0.70	-0.35
Channel Z - Input	-200.86	-1.06	0.53

2. Common mode sensitivity

DASY measurement parameters: Auto Zero Time: 3 sec; Measuring time: 3 sec

	Common mode Input Voltage (mV)	High Range Average Reading (μV)	Low Range Average Reading (μV)
Channel X	200	14.43	13.13
	- 200	-12.22	-13.72
Channel Y	200	-10.07	-9.78
	- 200	9.61	8.66
Channel Z	200	-0.56	-0.83
	- 200	-0.01	0.11

3. Channel separation

DASY measurement parameters: Auto Zero Time: 3 sec; Measuring time: 3 sec

	Input Voltage (mV)	Channel X (μV)	Channel Y (μV)	Channel Z (μV)
Channel X	200	-	3.08	0.09
Channel Y	200	3.19	-	4.59
Channel Z	200	0.90	-0.06	-

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4. AD-Converter Values with inputs shorted

DASY measurement parameters: Auto Zero Time: 3 sec; Measuring time: 3 sec

	High Range (LSB)	Low Range (LSB)
Channel X	15920	15519
Channel Y	16179	17567
Channel Z	15791	15270

5. Input Offset Measurement

DASY measurement parameters: Auto Zero Time: 3 sec; Measuring time: 3 sec

Input 10M Ω

	Average (μ V)	min. Offset (μ V)	max. Offset (μ V)	Std. Deviation (μ V)
Channel X	0.03	-1.16	2.66	0.46
Channel Y	-0.63	-3.22	0.29	0.46
Channel Z	-0.87	-2.03	0.28	0.46

6. Input Offset Current

Nominal Input circuitry offset current on all channels: <25fA

7. Input Resistance (Typical values for information)

	Zeroing (kOhm)	Measuring (MOhm)
Channel X	200	200
Channel Y	200	200
Channel Z	200	200

8. Low Battery Alarm Voltage (Typical values for information)

Typical values	Alarm Level (VDC)
Supply (+ Vcc)	+7.9
Supply (- Vcc)	-7.6

9. Power Consumption (Typical values for information)

Typical values	Switched off (mA)	Stand by (mA)	Transmitting (mA)
Supply (+ Vcc)	+0.01	+6	+14
Supply (- Vcc)	-0.01	-8	-9